NBS TECHNICAL NOTE 983

U.S. DEPARTMENT OF COMMERCE / National Bureau of Standards

Properties of Selected Superconductive Materials 1978 Supplement

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Properties of Selected Superconductive Materials 1978 Supplement

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(Extends Survey of Superconductive Materials and Critical Evaluation of Selected Properties, B. W. Roberts, J. Phys. Chem. Ref. Data 5, 581 (1976) and supersedes NBS Technical Note 825.)

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CONTENTS

PROPERTIES OF SELECTED SUPERCONDUCTIVE MATERIALS

1978 SUPPLEMENT*

B. W. Roberts

This report includes data on additional superconductive materials extracted from the world literature up to fall 1977 and is an addendum to the data set published in J. Phys. Chem. Ref. Data 5, #3, 581-821 (1976)(Reprint #84). The data presented are new values and have not been selected or compared to values (except for selected values of the elements) previously assembled by the Superconductive Materials Data Center. The properties included are composition, critical temperature, critical magnetic field, crystal structure and the results of negative experiments. Special tabulations of high magnetic field materials with Type II behavior and materials with organic components are included. All entries are keyed to the literature. A list of recent reviews centered on superconductive materials is included.

Key words: Bibliography; composition; critical fields; critical temperature; crystallographic data; data compilation; low temperature; superconductive materials; superconductivity.

INTRODUCTION

This Technical Note extends the data set on superconductive materials published in Journal of Physical and Chemical Reference Data 5, #3, 581-821 (1976)**. Because the world activity in the study of superconductive materials continues at a high rate a few hundred references are in hand awaiting translation or delivery of the original.

It is hoped that the users of these data will inform the author of needed corrections, deletions and additional information which may include unpublished results to be included and referenced under the contributor's name and/or institution.

BACKGROUND

Nearly seventy years of research on the phenomena of superconductivity has led to a substantial technical utilization in coils to produce large magnetic fields in special configurations. A major user and benefactor has been the very high energy particle physicist who by judicious choice and substitution of superconductive coils has been able to produce suitable magnetic fields to upgrade accelerators to the next round of particle energies. This substitution has been possible in an era of decreasing resources because of magnet size and operating power cost reduction. Other high field applications include test train car levitation in Japan and Germany, superconductive motors to test drive pumps and propel ocean vessels and recently the assignment of contracts to build three large prototype fusion reactor magnet sectors at about $\$5 \times 10^6$ each. The application to alternating current devices is progressing with larger prototype generators in the planning stages.

*This work has been partially supported by the NBS Office of Standard Reference Data.

**Available as Reprint #84 from the American Chemical Society, 1155 Sixteenth Street, N. W., Washington, D. C. 20036 at $12.50 U.S. prepaid.

Laboratory research magnets have attained 177 kG in a Nb_3Sn-V_3Ga assembly and 301 kG in a hybrid magnet.

On the micro scale a serious study is underway on the possible use of the Josephson junction in a computer with increased speeds of 2 or 3 orders of magnitude.

A series of superconductive temperature standards provided by NBS are gaining more widespread application.

Active study of superconductive materials continued throughout the world in anticipation of applications. The 1976 Applied Superconductivity Conference at Stanford University attracted 330 papers of which 230 are published in IEEE Transactions of Magnetics, Vol. MAG-13, No. 1, January 1977 (938 pages).

Prof. John Bardeen was denoted 1976 Scientist of the year by Industrial Research (See Ind. Res. pp. 37-42 Nov. 1976).

GENERAL PROPERTIES OF SUPERCONDUCTORS

The historically first observed and most distinctive property of a superconductive body is the near total loss of resistance at a critical temperature T_c characteristic of each material. Figure 1 illustrates schematically, two types of possible transitions. The sharp vertical discontinuity is indicative of that found for a single crystal of a very pure element or one of a few well annealed alloy compositions. The broad transition, illustrated by broken lines, is typical of the transition shape seen for materials which are inhomogeneous or contain unusual strain distributions. The temperature interval, over which the transition between the normal and superconductive states takes place, may be of the order of as little as 2×10^{-5} K or several K in width, depending upon the material state. The narrow transition width was observed in 99.9999% purity gallium single crystals.

Careful testing of the resistivity limit for superconductors has shown that it is less than 4×10^{-25} ohm-m, while the lowest normal state resistivity observed in metals is of the order of 10^{-15} ohm-m. Comparison of the resistivity of a superconductive body to that of copper at room temperature reveals that the superconductive body is at least 10^{17} times less resistive.

A Type I superconductive body, as exemplified by many pure metals, exhibits perfect diamagnetism (the Meissner state) below T_c and excludes a magnetic field up to some critical field H_c, whereupon it reverts to the normal state as shown in the H-T diagram of figure 1.

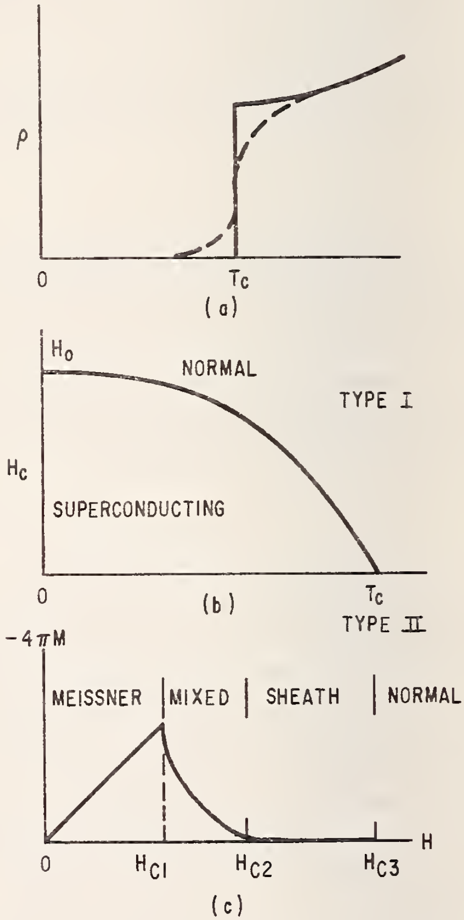

Figure 1. Physical properties of superconductors. (a) Resistivity versus temperature for a pure and perfect lattice (solid line). Impure and/or imperfect lattice (dashed line). (b) Magnetic field-temperature dependence for Type I or "soft" superconductor. (c) Schematic magnetization curve for "hard" or Type II superconductor

The discovery of the high-magnetic-field large-current-carrying capability of Nb_3Sn and other compounds and alloys has led to an extensive study of their physical properties. In brief, a high magnetic field superconductor, or Type II superconductor, passes from the perfect diamagnetic state at low magnetic fields to a mixed state and finally to a sheath state before attaining the normal resistive state of the metal. The magnetization of a typical high-field superconductor is shown in figure 1. The magnetic field values separating the four stages are given as H_{c1}, H_{c2}, and H_{c3}. The superconductive state below H_{c1} is perfectly diamagnetic and identical to the state of most pure metals of Type I. Between H_{c1} and H_{c2} a "mixed state" is found in which magnetic flux penetrates the superconductor in a nonuniform manner. Specifically, a lattice array of supercurrent vortices is formed, the magnetic flux contained within each vortex cell being equal to the magnetic flux quantum ($\sim 2 \times 10^{-7}$ gauss cm^2). At H_{c2} the fluxon density has become so great as to drive the interior volume of the material completely normal. Between H_{c2} and H_{c3} the superconductor has a sheath of current carrying superconductive material at its surface, and above H_{c3} the normal conducting state exists throughout the material. With careful measurement, it is possible to determine H_{c1}, H_{c2}, and H_{c3}. Table 4 contains data on high field superconductive materials.

A more complete representation of the states present in a high field superconductor is given in figure 2 with the additional phenomenon called fluctuation superconductivity. The latter phenomenon is evidenced in several physical properties above the appropriate critical fields and critical temperatures.

High field superconductive phenomena are also related to specimen dimension and configuration. For instance, the Type I superconductor, Hg, has entirely different magnetization behavior in high magnetic fields when contained in the very fine set of filamentary tunnels in an unprocessed Vycor glass. The great majority of superconductive materials are Type II. Most, but not all, elements in very pure form are Type I.

A further complication exists in the description of superconductive materials. In some instances a transition from Type II behavior to Type I behavior occurs as temperature is increased between absolute zero and T_c.

This survey has included the parameters T_c, H_c, H_{c1}, H_{c2}, H_{c3}, and has noted the crystal structure by code or crystal system. The values of H_c are sometimes noted to be taken at a specific temperature below T_c and denoted T_{obs}.

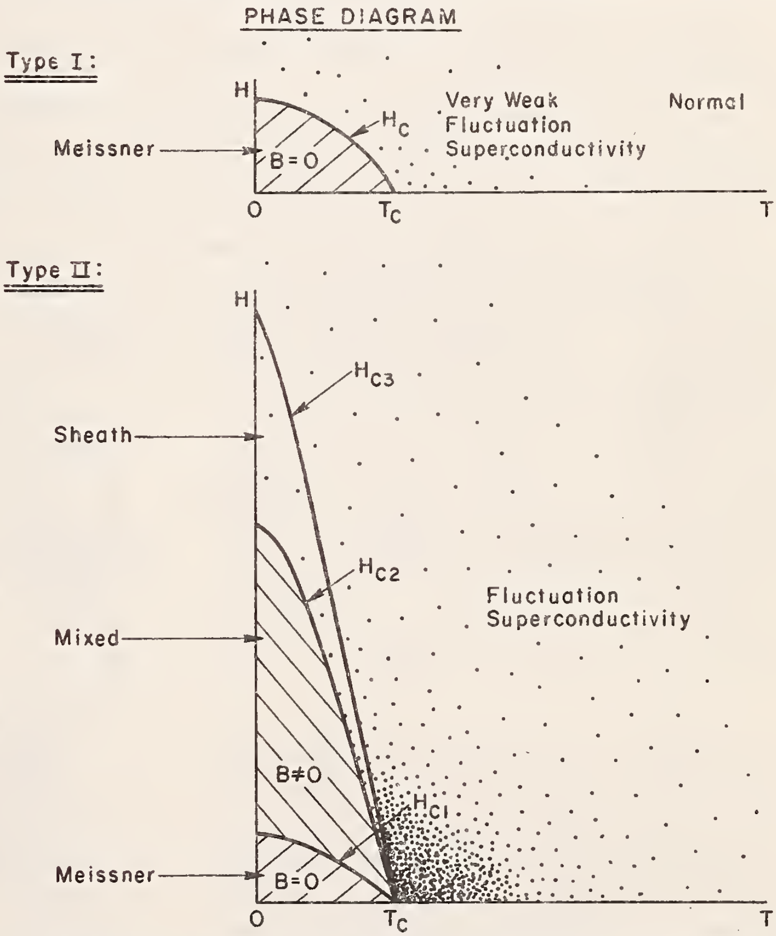

Figure 2. H-T phase diagram representation of Type I and Type II superconductors with locations for fluctuation superconductivity indicated. (R. R. Hake, personal communication and J. Applied Phys. 40, 5148 (1969). "The Thermodynamics of Type I and Type II Superconductors.")

H_0 is H_c extrapolated to 0 K. Methods of extrapolation are critical in the case of high-magnetic-field parameters H_{c1}, H_{c2}, and H_{c3}.

The metallurgy, chemistry, and physics of superconductors is a complex and sometimes subtle subject. Therefore, readers are referred to the many texts and review articles listed in Reprint #84 and the "Recent Reviews" section of this report for complete and additional information. "Superconductivity" by E. A. Lynton (Metheun and Co., London; John Wiley and Co., New York) is a brief and useful introduction. For additional general information see "Superconducting Materials" by E. M. Savitskii, V. V. Baron, Yu. V. Efimov, M. I. Bychkova, and L. F. Myzenkova (Plenum Press, New York-London, 1973); an updated translation of "Metallovedenie Sverkhprovodyashchikh Materialov" (Nauka Press, Moscow, 1969); "The Science and Technology of Superconductivity" Vol. 1 and 2, edited by W. D. Gregory, W. N. Mathews, Jr., and E. A. Edelsack (Plenum, New York-London, 1973) and "The Effect of Metallurgical Variables on Superconducting Properties", J. D. Livingston and H. W. Schadler in Progr. Materials Sci. (G. B.), Vol. 12, No. 3, 185-274 (1964). For theoretical aspects start with "Superconductivity", Vols. 1 and 2, edited by R. D. Parks, (Marcel Dekker, New York, 1969).

NEW DEVELOPMENTS IN SUPERCONDUCTIVE MATERIALS

The discovery of the high probability of superconductivity in the Chevrel phases, M Mo_6S_8, where M is a metallic atom, has broadened to 51 entries in Table 2. The highest T_c reported is 14.7K for $PbMo_6S_8$, and even though lower than the highest T_c in A-15 compounds, the critical fields have been found to be 50% higher (see Figure 3). A modification, $PbGd_{0.2}Mo_6S_8$, has an H_{c2} at 0K of greater than 600kG. (See Science 196, 966-8, 1977.)

A series of ternary borides has been described of form $(RE)Rh_4B_4$ with critical temperatures in the range of 2.5 to 11.9K where (RE) denotes a rare earth element. And most exciting is the discovery that $ErRh_4B_4$ of the series is the first single phase re-entrant superconductor which is normal to 8.7K, superconductive from 8.7 to 0.9K and ferri-magnetic below 0.9K. Careful study of this system should answer several of the scientific puzzles in relating the superconductive and magnetic states (Science 196, 966-8 (1977) and B. T. Matthias, E. Corenzwit, J. M. Vandenberg and H. E. Barz, Proc. Nat. Acad. Sci., USA 74, 1334-5 (1977)).

A tantalizing observation in the Nb_3Ge preparation series suggests further careful study. R. D. Blaugher (to be published) has observed an onset T_c of 25.6K in a single Nb_3Ge film annealed for a substantial time. Efforts to reproduce the properties have not been successful and are still underway. Blaugher believes that the sample with the 25.6 K critical temperature will be reproduced and that it is part of a distribution dependent upon subtle composition or preparation variables.

A series of studies have developed a "standard" curve of T_c decrease as a function of irradiation

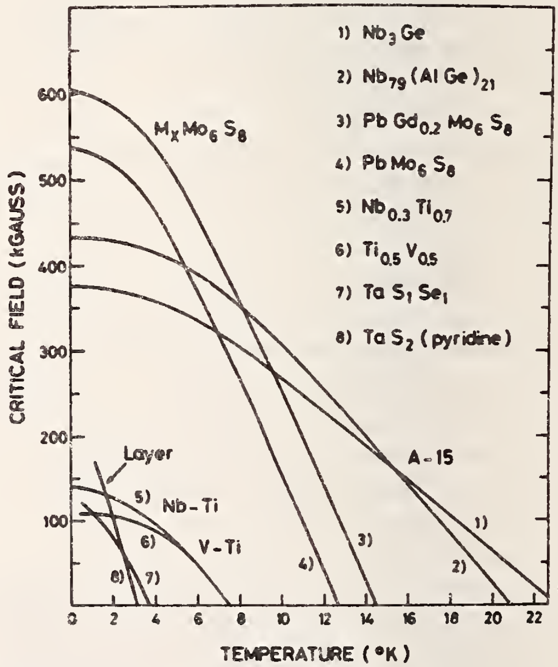

Figure 3. Critical magnetic fields versus temperature for selected superconductive materials. (From Oe. Fischer, Low Temp. Phys. - LT14. Ed. M. Krusius and M. Vuorio (Amer. Elsevier, N. Y., 1975). Vol. V, page 188).

level in the A15 compounds. In some instances, total recovery of T_c has been observed upon annealing.

Thorough investigation of $(SN)_x$ by several experimental techniques has shown it to be a three dimensional superconductive material with anisotropic properties.

A definitive correlation of the T_c's of 28 A15 (A_3B) compounds with the phase diagram solid solution range has been reported. Two groupings are found--those with ranges only on the A-rich side and those extending on both sides or only on the B-rich side. (F. E. Wang, to be published.)

Nb_3Ge films with high critical temperatures have been found to require oxygen in their preparation or in their final composition. How the oxygen enhances the material properties has apparently not been specified (see $GeNb_3O_x$ entries in Table 2).

A "round robin" testing for T_c of sputtered Nb_3Ge films has been reported. The midpoint of the superconductive transition was found to be the most reproducible (see R. Roy and D. A. Rogowski, Phys. Letters 57A, 60-62 (1976)).

Carlo Reale has claimed novel superconductive material results for quench condensed thin films in several papers: Vacuum 27, 3-6 (1977); J. Low Temp. Phys. 24, 289-95 (1976); Appl. Phys. Letters 27, 157-8 (1975); Thin Solid Films 28, L29-30 (1975);† Acta Physica Acad. Sci. Hung. 37, 53-60 (1974); Phys. Letters 57A, 65-6 (1976); 55A, 165 (1975)† and 51A, 353-4 (1975)†. A selection of his reported findings are listed in Table A with film thickness range and are compared to literature data as well as recent negative experimental data of N. Jacobsen, C. G. Granqvist and T. Claeson (Z. Physik B25, 265-8 (1976))‡ and M. Belzons, R. Blanc and R. Payan, C.R. Acad. Sc. Paris 283B, 241-4 (1976) in reference to magnesium.

Table A. Comparison of T_c determinations for some alkali metals, alkaline earth metals and lanthanides. (After Jacobsen, Granqvist and Claeson)

	Results by Reale (†)		Literature Data	This Investigation‡	
Metal	T_c[K]	Thickness [Å]	T_c[K]	T_c[K]	Thickness [Å]
Li	2.4-1.1	100-2000			
Be	9.2-3.7	100-2000	6-9.95		
Mg	5.5	100	< 0.35	< 0.32	200,300
				< 1.5	
Ca	4.3	100	< 2		
Sr	3.6	100	< 2		
Cs	1.05-0.4	100-2000			
Ba	3.0	100		< 0.35	100-1000
La	9.8-6.8	100-2100	4.5		
Ce	5.8-3.0	100-2100	< 1.5	< 0.32	200-700
Pr	5.0-2.5	100-2100		< 0.33	200-1000
Nd	4.6-2.1	100-2100		< 0.33	300
Eu	3.4-1.7	100-2100			
Yb	2.9-1.4	100-2100	< 1.5	< 0.35	200-600

A new type of "superconducting domain" in a bulk insulating state has been claimed to explain several electrical and magnetic measurements in compounds such as sodium dioxycholate and sodium cholinate. Changes in properties are observed at temperatures up to 277K for the latter (see Proc. IEEE, March 1976, pp. 357-359 and Physiol. Chem. Phys. 8, 135-42 (1976)).

Intensive study of a variety of organic compounds such as (TTF)(TCNQ) and (TSeF)(TCNQ) has continued. The latter is one of the most electrically conductive materials discovered. At room temperature it has a conductivity of 800 $(\text{ohm-cm})^{-1}$ and a peak value at 40K. A superconductive organic material has not been claimed. (IBM Research Highlights, October, 1975) (Chemical and Engineering News July 4, 1977, pp. 14-17.)

The calibration and the standardization of techniques and temperatures for the measurement of superconductive critical temperatures has been widely accepted and continues the work of R. J. Soulen, Jr. and J. H. Colwell (J. Low Temp. Phys. 5, 325 (1971)) and J. F. Schooley and R. J. Soulen, Jr. (Proc. 12th Intern. Conf. on Low Temp. Phys. (Academic Press of Japan, Tokyo, 1971) and the XIII Inter. Congress of Refrigeration, pp. 192-198). They have carefully measured, compared and tested the reproducibility and width of the critical temperature of Pb, In, Al, Zn and Cd for thermometric fixed points as well as having looked very carefully at the equivalence of the transition temperature when measured by the three techniques: (1) Electrical resistance, (2) magnetic susceptibility and (3) heat-capacity measurements. In the case of well-annealed polycrystalline and pure (99.999%) indium they find that the midpoints of each type transition are identical to within 0.1 mK. Arrangements have been made to provide cryogenic experimenters with samples and devices through the NBS Office of Standard Reference Materials. (NBS Special Publication 260-44, "Preparation and Use of Superconductive Fixed Point Devices SRM 767." Superintendent of Documents, U. S. Government Printing Office, Washington, D. C. 20402. (Order by SD Catalog No. C13.10:260-44.) Price 75 cents.)

The sensitivity of superconductive properties to the material state is most pronounced and has been used on occasion in the reverse to study and specify the detailed state of alloys. The mechanical state, the homogeneity, and the presence of impurity atoms and other electron-scattering centers are all capable of controlling the critical temperature, critical field, and the current-carrying capabilities in high magnetic fields. Well-annealed specimens usually show sharper transitions than those that are strained or inhomogeneous. This sensitivity to mechanical state underlies a general problem in the tabulation of properties of superconductive materials. The occasional divergent values of the critical temperature and of the critical fields quoted for a Type II superconductor may lie in the variation in sample preparation. Critical temperatures of materials studied early in the history of superconductivity must be evaluated in light of the probable metallurgical state of the material as well as the availability of less-pure starting elements. It has been noted that recent work has given extended consideration to the metallurgical aspects of sample preparation as well as to ingenious application of new and exotic materials preparation techniques to obtain the desired high critical temperatures and high critical magnetic fields. Figure 4 outlines the onset critical temperature as a function of the effective quenching or cooling rate for Nb_3Ge alloys as research exploration continued to yield higher and higher values of T_c. See the section on new developments for further comment on the Nb_3Ge system.

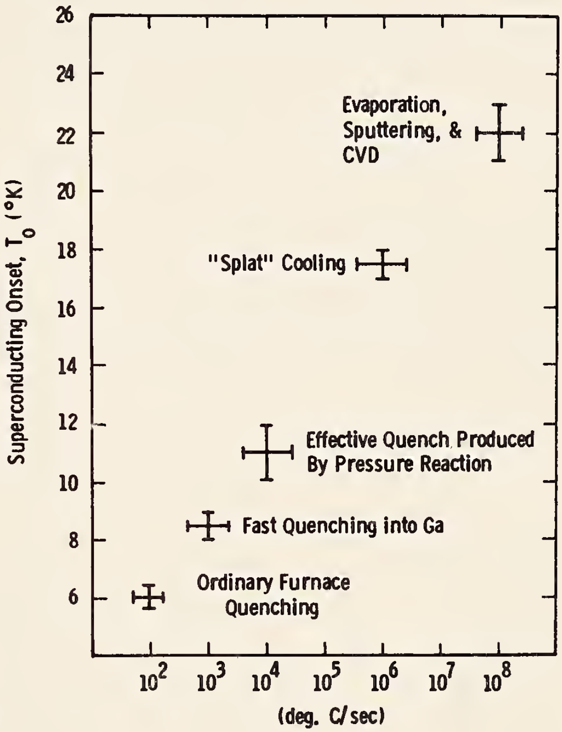

Figure 4. Onset critical temperature as function of quenching or cooling rate of various Nb_3Ge preparations (From R. D. Blaugher, IEEE Trans. Magn. MAG-13, 821 (1977)).

HOW TO USE THE DATA TABLES*

Properties of the superconductive elements are covered in table 1(a) for bulk values, 1(b) for thin-film preparations, and 1(c) for high-pressure modifications and metastable forms prepared by the application of high pressure.

Metallic and inorganic materials including the elements are listed and referenced in table 2 except that superconductive materials with organic and related constituents are cited in table 3.

Tables 1 through 3 contain references to "HF" signifying that critical magnetic-field data H_{c1}, H_{c2}, or H_{c3} are reported in table 4 with appropriate references to the literature.

Tables 2 through 4 list the bulk material values for alloy systems first, then results of special studies such as pressure or dispersal in porous media, and finally, thin-film data with notations of temperature of deposition and film thickness in Angstroms(Å).

The probable error limits are given for most of the bulk elements in table 1(a) and are derived from all the values collected in the data set. The procedure to determine error limits included the assembly of all acquired data on an element. Where possible, a selection was made of data obtained on samples with recorded high purity. If a sufficient number of values were available, the standard deviation was determined and listed. Error limits in a few instances were increased over the standard deviation if the element was known to be difficult of purification.

Tables 2-3 contain data on negative experiments in the column headed "T_n", which is the temperature in K down to which the material has been checked specifically for a superconductive transition without success. If a material has been found to be only ferrimagnetic, antiferromagnetic, or ferromagnetic it has not been included in this survey.

All compositions are denoted on an atomic basis; i.e., one atomic weight of A and one of B to form the AB composition. Exceptions are noted. Solid solutions or a range of compositions may be denoted as $A_{1-x}B_x$ or $A_xB_yC_{1-x-y}$, or by the actual atomic fraction range such as $A_{1-0.4}B_{0-0.6}$. The critical temperature or magnetic fields may then be denoted either by a range of values or a maximum value (Max.).

A continuing point of difficulty lies in the method of selecting T_c from an experimental transition measurement whether it be the change in effective permeability, resistance, optical reflectivity, electron diffraction signal, specific heat or ultrasonic absorption. Most authors choose the midpoint of the curve (fig. 1(a)), but in the search for very high T_c materials often the "onset" temperature is chosen as the critical temperature. Some authors quote the width of the transition, and where a single alloy and single reference is given a range in T_c denotes the upper and lower limits to the transition.

Table 3 contains those special superconductive materials containing organic constituents. Most of the entries are layered compounds with an intercalated organic substance. These special materials exhibit both two- and three-dimensional superconductivity and have highly anisotropic high magnetic field properties.

In some instances a single line in a table will summarize the discoveries and measurements of two or three full research papers. It is therefore probable and reasonable for the researcher to explore the original references to obtain a full background of the abstracted data.

For problems in solders for low-temperature research, the paper by W. H. Warren, Jr. and W. G. Bader (Rev. Sci. Instruments 40, 180 (1969) is useful. Also see Meijer, H. C., Bots, G.J.C. and Coops, G. M. Proc. of Sixth Inter. Cryogenic Eng. Cong. (Paper K11) 6, 404-5 (1976).

*The NBS Office of Standard Reference Data, as administrator of the National Standard Reference Data System, has officially adopted the use of SI units for all NSRDS publications, in accordance with NBS practice. This publication does not use SI units uniformly because contractual commitments with the author predate establishment of a firm policy on their use by NBS. Some appropriate conversion factors will be found in Tables 1 and 2. We urge that specialists and other users of data in this field accustom themselves to SI units as rapidly as possible.

SYMBOLS AND ABBREVIATIONS (RELATING TO TABLES 1 TO 4)

T_n	The lowest temperature to which a material has been tested with negative results for a transition to the superconductive state.
∇	Given in front of reference number, it denotes a thin-film study.
#	After a reference number indicates electronic specific heat, Debye theta or related parameter values are given in the reference. See end of table 1(a) for general references to these data.
n, p	Denotes the number of carriers per cubic centimeter in semiconductors that exhibit a superconductive state at very low temperature.
$T_c'(\ldots)$	Denotes incremental changes in temperature (K) from T_c of the pure metal. For example, T_c' (+0.05) denotes that two or more measurements have been made by adding a small amount of alloying element to a metal to form a dilute alloy (or mixture) and in so doing T_c has been raised by 0.05K. T_c' (-0.03+0.14) denotes an initial decrease and then an increase to 0.14K over the pure metal.
P	Denotes pressure (quoted in kbar; may be rounded units of katm or other unit).
ppm	Parts per million.
T_{obs}	Denotes temperature of observation of H_c, H_{c1}, H_{c2}, and H_{c3}.
oersted	Is equivalent to 79.57 amperes/meter.
RRR	Denotes "residual resistivity ratio" and is used only as an indicator of sample purity. In most instances it is the room temperature resistivity divided by the resistivity at 4.2K. The original reference should be consulted for details.
Å	Denotes 10^{-10} m or 10^{-8} cm or one Angstrom unit.
Max.	Indicates that the value given is the maximum value of 3 or more measured values of a variable.

Crystallographic System Abbreviations

CUB	Cubic
TET	Tetragonal
HEX	Hexagonal
ORTHO	Orthorhombic
MONO	Monoclinic
RHOMB	Rhombohedral (sometimes described in hexagonal format)
TRI	Triclinic

The "Strukturbericht" types are described in W. B. Pearson, Handbook of Lattice Spacings and Structures of Metals (Pergamon, New York, 1958), p. 79, also Vol. II (Pergamon, New York, 1967) p. 3. A condensed set is also presented in Reprint #84 (see abstract for this report.).

ACKNOWLEDGMENTS

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The continued excellent assistance of Miss Vera Chase, Chief Research Librarian, and Miss Judy Lent and all of our fine library staff is gratefully acknowledged. Works on superconductivity are found in unusual and extraneous publications.

Mrs. Mary Dean has steadfastly and resolutely set up and typed the very long tables and difficult material of this report and D. N. Wemple has proofread much of it.

TABLE 1(a). Properties of the Superconductive Elements (See Table 2 for recent References, Crystal Structure Data, and Parameters of Non-Superconductive Elements where tested).

Element	T_c(K)	H_o(oersted)	θ_D(K)[b]	γ($mJmol^{-1}K^{-1}$)[b]
Al	1.75±0.002	104.9±0.3	420	1.35
Am* (α,?)	0.6			
Am* (β,?)	1.0			
Be	0.026			0.21
Cd	0.517±0.002	28±1	209	0.69
Ga	1.083±0.001	58.3±0.2	325	0.60
Ga (β)	5.9,6.2	560		
Ga (γ)	7	950,HF[a]		
Ga (Δ)	7.85	815,HF		
Hf	0.128	12.7		2.21
Hg(α)	4.154±0.001	411±2	87,71.9	1.81
Hg (β)	3.949	339	93	1.37
In	3.408±0.001	281.5±2	109	1.672
Ir	0.1125±0.001	16±0.05	425	3.19
La (α)	4.88±0.02	800±10	151	9.8
La (β)	6.00±0.1	1096,1600	139	11.3
Lu	0.1±0.03	350±50		
Mo	0.915±0.005	96±3	460	1.83
Nb	9.25±0.02	2060±50,HF	276	7.80
Os	0.66±0.03	70	500	2.35
Pa	1.4			
Pb	7.196±0.006	803±1	96	3.1
Re	1.697±0.006	200±5	4.5	2.35
Ru	0.49±0.015	69±2	580	2.8
Sn	3.722±0.001	305±2	195	1.78
Ta	4.47±0.04	829±6	258	6.15
Tc	7.8±0.1	1410,HF	411	6.28
Th	1.38±0.02	160±3	165	4.32
Ti	0.40±0.04	56	415	3.3
Tl	2.38±0.02	178±2	78.5	1.47
V	5.40±0.05	1408	383	9.82
W	0.0154±0.0005	1.15±0.03	383	0.90

*J.L. Smith and R.G. Haire, Science 200, 535-6 (1978).

TABLE 1(a)(continued)

Element	T_c(K)	H_o(oersted)	θ_D(K)[b]	γ($mJmol^{-1}K^{-1}$)[b]
Zn	0.85±0.01	54±0.3	310	0.66
Zr	0.61±0.15	47	290	2.77
Zr (ω)	0.65, 0.95			

[a]HF denotes high field superconductive properties. See Table 4 for recent values.
[b]For a complete data set, see Phillips, N. E., Critical Reviews in Solid State Sciences 2, 467-554 (1972), "Low Temperature Heat Capacity of Metals." Also Mendelssohn, K., in Cryophysics (Interscience, New York, 1960), p. 178, Gschneidner, K. A. Jr., in Solid State Physics 16, 275-426 (1964), Parkinson, D. H., Rep. Progr. Phys. 21, 226 (1958) and Heiniger, F., Bucher, E., and Muller, J. "Low Temperature Specific Heat of Transition Metals and Alloys" Phys. Kondens. Materie 5, 243-284 (1966).

TABLE 1(b). Range of Critical Temperatures Observed for Superconductive Elements in Thin Films Condensed Usually at Low Temperatures (See Table 2 for Recent Data and References and Table 4 for "HF" Critical Magnetic Field Property Data)

Element	T_c Range (K)	H_o(oersted)
Al	1.15-~5.7	HF[a]
Be	5-9.75	HF
Bi	6.17-2.6	
Cd		
(Disordered)	0.79-0.91	
(Ordered)	0.53-0.59	
Ga	2.5-8.5	HF
Hg	3.87-4.5	
In	2.2-5.6	HF
La	3.55-6.74	
Mo	3.3-8.0	
Nb	2.0-10.1	
Pb	1.8-7.5	
Re	1.7-~7	
Sn	3.5-~6	

TABLE 1(b)(continued)

Element	T_c Range (K)	H_o(oersted)
Ta	< 1.7-4.51	HF
Tc	4.6-7.7	
Ti	1.3 Max	
Tl	2.33-2.96	
V	1.8-6.02	
W	< 1.0-4.1	
Zn	0.77-1.70,~1.9	

[a]HF denotes high magnetic field superconductive properties in Table 4.

TABLE 1(c). Elements Exhibiting Superconductivity Under or After Application of High Pressure (See Table 2 for Recent References, Table 4 for "HF" Critical Magnetic Field Properties)

Element	T_c Range (K)	Pressure (kbar)[b]
Al	1.98-0.075	0-62
As	0.31-0.5	220-140
	0.2-0.25	~140-100
Ba II	~1-1.8	~55-85
III	1.8-5	~85-144
IV	4.5-5.4	144-190
Bi II	3.9	25-27
III	6.55-7.25	28-38
IV	7.0,8.7-6.0	43,43-62
V	6.7,8.3	48-80
VI	8.55	90,92-101
VII(?)	8.2	30
Ce (α)	0.020-0.045	20-35
Ce (α')	1.9-1.3	45-125
Cs V	~1.5	>125
Ga II	6.38	≥35
II'	7.5	≥35 then P removed
Ge	5.35	115
La	~5.5-12.9	0-210
Lu	0.022-1.0	45-190
P	5.8	170
Pb II	3.55	160
Re II	2.3 Max.	"Plastic" compression
Sb(Prepared 120 kbar, held below 77K)	2.6-2.7	
Sb III	3.55-3.40	85-~150
Se II	6.75,6.95	~130
Si	6.7-7.1	120-130

TABLE 1(c)(continued).

Element	T_c Range(K)	Pressure(kbar)[b]
Sn II	5.2-4.85	125-160
III	5.30	113
Te II	2.4-5.1	38-55
III	4.1-4.2	~53-62
IV	4.72-4	63-80
( )	3.3-2.8	100-260
Tl(cubic form)	1.45	35
(hexagonal form)	1.95	35
U	2.4-0.4	10-85
Y	2.3-1.7-2.5	110-125-160
Zr (omega form, metastable)	1-1.7	60-~130

[b] 1 kbar = 10^8 newton/meter^2 = 0.987 katm

TABLE 2. Properties of Superconductive Materials (including those proven non-superconductive)

Note: "HF" signifies critical magnetic field data in Table IV.

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Ag					2070
$Ag_{0.82}Al_{0.18}$	0.022				2147
$AgBi_{0-0.8}Se_2Sn_{1-0.2}$	5.68-5.68, 5.81-5.82				2411
$Ag_{0-0.4}DxPd_{1-0.6}$ (Implant)	10-14.5-4				2347
$Ag_{0.895-0.828}Ga_{0.105-0.172}$	0.0065-0.116				2070
$Ag_{0.92}Ge_{0.08}$	0.0248				2147
$Ag_{0.5}Ge_{0.5}$ (Quench condensed)	1.2				∇2365
$Ag_{0.5}Ge_{0.5}Kr_x$ (Implant)	2.5 (Quench condensed)				∇2365
$Ag_{0-0.4}H_xPd_{1-0.6}$ (Implant)	9-15-9				2347
$Ag_{0.05}H_{0.8-0.89}Pd$	2.2-4.3				2325
$Ag_{0.1-0.34}H_{0.5-0.85}Pd$				1.4	2325
$Ag_{0.81}In_{0.19}$	0.0074				2070
AgLu			B2	0.04	2006
$AgMo_4S_5$	8.9		RHOMB		2287
$Ag_{0-0.02}Nb_{0.33}Ti_{0.66}$		HF			2262
$AgS_{0.2}Se_{1.8}Sn$	5.90-5.55(Quenched) 5.79-5.72(Plus 400C)		B1		2411
$Ag_{0.9}S_{0.2}Se_{1.8}Sn_{1.1}$	6.79-6.54		B1		2411
$AgSb_{1-0}Se_2Sn_{0-1}$	<1.5-5.5		B1		2411
AgSc			B2	0.04	2006
$Ag_{1.1-0.7}Se_2Sn_{0.9-1.3}$	4.6-6.9-6.5 (Quenched) 4.5-4.5-5.6-5.5 (Annealed) 6.2-6.5 (Anneal 500C)		B1		2411
$AgSe_2Sn$	4.71		B1		2411
$Ag_{1-0.81}Se_2Sn_{1-1.19}$	4.71-6.47 ($n = 1.1-1.7x10^{22}$)		B1		2411
$Ag_{1-0.8}Se_{2.1-1.9}Sn_{1-1.2}$	6.96-5.4				2411
$Ag_{0.8}Se_{1.9}Sn_{1.2}$	6.96		B1		2411
$Ag_{0.8}SeSn_{1.2}$	6.75		B1		2411
AgY			B2	0.04	2006

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Ag_{0.70}Zn_{0.30}$	0.0125				2070
$Ag_{0.265}Zn_{0.735}$	0.18				2278#
$Ag_{0.205}Zn_{0.775}$	0.17				2278#
$Ag_{0.155}Zn_{0.845}$	0.090				2278#
$Ag_{0.125}Zn_{0.875}$	0.100				2278#
$Ag_{0.13-0.305}Zn_{0.87-0.695}$	0.10-0.09-0.19		HEX		2279#
Al(150-50A diam.)	1.5-2.5				2294
Al(100A diam.)	1.68				2064
Al(P=0-62k bar)	1.18-0.075				2043
Al(Implants of O_2,He,H, D and Al)					∇2015
Al(Al implant,)(1500A) 10K	2.6 Max.				∇2015
Al (350A)	3.46				∇2230
Al (380-1400A)	1.42-2.37 (T_c ∿ to grain size)		A1		∇2270
Al (1000A; deposited 4.2K)	1.3				∇2160
Al (70-450A)	2.83-2.67				∇2199
Al (SiO_2 coating)	2.83-3.7				∇2199
Al (RRR ∿2000)	1.180; 1.175				∇2387
Al (Ar) (350A plus)	4.2-3.1				∇2230
$Al_{0.04-0.14}Au_{0.96-0.86}$	0.008-0.385		CUB		2070
$AlAu_2La$			B2	0.04	2006
$AlAu_2Sc$	4.40		B2		2006
$AlAu_2Y$			B2	0.04	2006
$Al_{0.8}B_{0-\sim0.1}Ge_{0.2}Nb_3$	19-18 (As cast) 19.4-18 (900C/14 days) 17-12-18 (Rapid quench)		A15		2053
$Al_{0-1}Be_{1-0}$ (Quenched < 6.6K; 125-255A)	8.8-6.0-5.6				∇2264
$Al_{0.3}Be_{0.7}$(Quenched < 2K)	Data given				∇2307
$Al_{\sim0.75}C_{\sim0.25}$(Implant:) 500-1000A	4.2				∇2296

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Al_{0.8}C_{0-\sim 0.1}Ge_{0.2}Nb_3$	18.5-18 (As cast) 17-17.5-16.5(900C/14 days) 17-19.3-14 (Rapid quench		A15		2053
$Al_2Ce_{0.00626}La_{0.994}$ (Re-entrant)	1.3(T_{c2} = 0.15)	HF			2098
$Al_2Ce_{0.0064}La_{0.9936}$ (Re-entrant)	1.1(T_{c2} = 0.25)				2055
$Al_2Ce_{0-0.0066}La$	3.3-∿1.5				2332
$Al_2Ce_{0.0066-0.009}La$ (Re-entrant)	∿1.5-0.2	HF			2332
$Al_2Ce_{0-0.906}La_{0.991}$				0.3	2055
$AlCe_{0.018}La_{2.982}$				0.02	2333
$AlCe_{0-0.017}La_{3-2.983}$	6-0.8	HF			2333#
$AlCr_{0-0.015}Nb_3$	Data given		A15		2322
$Al_{0.7}D_{0.3}$(1000A; deposited 4.2K)	5.7				∇2160
$AlFe_{0-0.06}Nb_3$	Tc/T_{co} = 1-0.95		A15		2322
$Al_{0.24}Ga_{0.05}Ge_{0.05}Nb_{0.69}$	18.35 (As cast) 19.4 (700C/3 weeks) 20.0 (700C/4 weeks)		A15		2305
$Al_{1-0}Ga_{0-1}Ge_{1-0}Nb_3$	20.4-6.1		A15		2305
$Al_{0.05-0.29}Ga_{0.05-0.2}Nb_{0.67-0.85}$	9.8-19		A15,Nb_5Ga_3+$D8_b$		2004
$Al_{0.175}Ga_{0.075}Nb_{0.75}$	19.0		A15,$D8_b$		2004
$Al_{0.15}Ga_{0.05}Nb_{0.80}$	17.8		A15		2004
$Al_{0.285}Ga_{0.05}Nb_{0.665}$			$D8_b$	4.2	2004
$Al_{1-0}Ga_{0-1}Nb_3$(co-sputtered)	16-14.5		A15		∇2067
$Al_{0.1-0.85}Ga_{0.9-0.15}V_3$	12.9-10		A15		∇2069
$Al_{0-0.08}Ga_{0.2-0.12}V_3$	15-14.1	HF			2010
$Al_{10.5}Ga_{0.1}V$	1.60-1.64				2363
$Al_{9.9}Ga_{0.1}V$	1.5-1.8				2363
$Al_{9.9}Ga_{0.1}V$	(No anneal)			1.3	2363
$Al_{10.5}Ga_{0.1}V$	(No anneal)			1.3	2363
$AlGd_{0-0.009}La_{3-2.991}$	6-0.9				2333
$Al_2Gd_{0.0038}La_{0.996}$	1.728				2057

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Al_{\sim 0.75}Ge_{\sim 0.25}$(Implant, 500-1000A)	7.35, 6.2				∇2296
$Al_{1-0}Ge_{0-1}Nb_3$	18.7-20-12 (Rapid quench) 18.7-20-6.5 (As cast, annealed)				2268, 2258
$Al_{1-0.91}Ge_{0-0.09}Nb$	18.6-20-19.7		A15		2323, 2019
$Al_{0.8}Ge_{0.2}Nb_3$	19.7 (1000K/110 hrs.)				2130#
$Al_{0.8}Ge_{0.2}Nb_3$	18.5 (Arc melted powder)				2130#
$Al_{0.6}Ge_{0.4}Nb_3$	16.8 Max.(750C/ 1hr-20days)		A15		2113, 2180
$Al_{0.75}Ge_{0.25}Nb_3$ (Sputter deposited)	18.5 Max.(750C/ 1 day) 15.9 Max.(1240C/ 2 hr; 750/20 days) 16.5 Max.(Same, deposited 485C)		A15		2113
$Al_{0.81}Ge_{0.29}Nb_{4.15}$(Sputter deposited, 200C)	18.5-7.9 (Various treatments)		A15		2113
	14.7-15.5 (1240C/4 hr; 750C/20 days)		A15		2113
$Al_{0.84}Ge_{0.16}Nb_{2.52}$(Sputter deposited)	16.9-17.2 (750C/5 days)				2133
$AlGeNb_3$	19.8 (Powder prep.)		A15		2259
$Al_{0.2-0.9}Ge_{0.8-0.1}Nb$ (Co-sputtered)	13-16.5-15.5		A15		∇2067
$Al_{0.9-0.1}Ge_{0.1-0.9}V_3$	12.5 Max.				2157
$Al_{0.1-0.85}Ge_{0.9-0.15}V_3$	4.5-9.7-11.2		A15		∇2069
$AlH_{\sim 2}$(Implant; 10K;1650A)	6.75 Max.				∇2015
$Al_{0.7}H_{0.3}$ (1000A; deposited 4.2K)	5.95				∇2160
$Al(H_2)$(350A of Al)	4.8-4.2				∇2230
Al(He)(Implant)	3.7 Max.				∇2015
$AlHf_{0-0.12}Nb_{3-2.88}$	18.6-15.2		A15		2323
Al(In)(280A,185A)	2.282, 3.178	HF			∇2211
$Al_{0-0.44}Ir_{0-0.40}Nb_{0.91-0.54}$	16.84- < 2				2003

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Al_{0.20}Ir_{0.025}Nb_{0.77}$	14.56				2003
Al_2La	3.273				2057
Al_2La	3.3	HF			2332
$Al_{1-0.92}Mg_{0-0.08}$	T_c'(-0.08+0.11)				2311
$Al_{0.2-0.08}Mg_{0.8-0.2}$(50-1000A)	∿4- < 0.32				∇2192
$Al_{0.1}Mg_{0.9}$(50-1000A)				Not Super-conductive	∇2192
Al_xMo (Implant)				1.2	2382
$AlMo_{0-0.30}Nb_{3-2.70}$	18.6-12.3		A15		2323
$Al_{0-0.6}Mo_{6.35}S_8Sn_{1.2}$	11.8-14.3	HF			2408, 2089
$Al_{0-0.03}Mo_{0.05-0.05}Ti_{0.95-0.92}$	3.197-2.7				2340#
$Al_{0-0.03}Mo_{0.05}Ti_{0.95}$($\alpha$' phase)	1-3.1-2.7				2152
$Al_{0-0.06}Mo_{0.25}Ti_{0.75}$($\beta$ phase)	3.8-2.1				2152
$Al_{0-0.03}Mo_{0.1}Ti_{0.9}$($\omega$+$\beta$ phases)	3.45-3.2				2152
$Al_{0.15-0.30}Nb_{0.85-0.70}$	15-18.8-10 17.0-11.7 (Liquid quenched)				2245, 2166
$Al_{0.235-0.29}Nb_{0.765-0.71}$	17.5-19-18.4		A15		2150
$Al_{0-0.07}Nb_{1-0.93}$			B2		2002
$Al_{0.1-0.42}Nb_{0.9-0.58}$	8.7-10-17.5-13- < 4.2				2002
$Al_{0-0.15}Nb_{1-0.85}$	9.03-5.15 (Cast) 8.8-8.1-10 (1750C/25 Hr)	HF	B2		2049
$AlNb_3$	18.5				2272#, 2180, 2131, 2258
$AlNb_3$	17.43 (As cast) 18.53 (Annealed)		A15		2075
$AlNb_3$	≃17.5	HF	A15		2193
$Al_{0.21}Nb_{0.79}$	16.84		A15		2003
$Al_{0.22}Nb_{0.78}$	∿15		A15		2002
$AlNb_2$	0.74	HF	$D8_b$		2170, 2193 2002 1810

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Al_{0.45-0.40}Nb_{0.55-0.60}$			$D8_b$	1.3	1810
Al_3Nb	0.64	HF	DO_{22}		2170, 2002
$AlNb_3$(Sputter deposit)	15.2-17.5 (1 hr-20 days/750C)		A15		2113
$AlNb_{2.33}$(Sputter deposit)	15.1-15.9 (750C/5 days)				2113
$Al_{\sim 0.15-0.3}Nb_{0.85-0.7}$ (Co-sputtered)	12.5-∿17		A15		▽2067
$AlNb_3$(Neutron irradiated)	18.6- < 1.4		A15		2216, 2285, 2190, 2019
$AlNb_3Ni_{0-0.05}$	$\frac{T_c}{T_{co}}$ = 1-1.04-0.85		A15		2322
$Al_{0.85-0.1}Nb_3P_{0.15-0.9}$ (Sputtered)	11.5-6.5-5				▽2067
$Al_{1-0.90}NbSe_{0-0.10}$	18.6-17.5		A15		2323
$Al_{0.04-0.10}NbSe_2$	5.4-1.1		HEX		2210
$AlNb_3Si_{0-\sim 0.1}$	17-19.1-17.5(As cast) 19.1-18.8-19(900C/14 days) 16-15-15.5(Rapid Quench) 15-13.5-12.5(Rapid Quench)		A15		2053
$Al_{1-0.93}NbSi_{0-0.07}$	18.6-18.4		A15		2323
$Al_{0.255}Nb_{0.73}Si_{0.015}$	∿16 (Liquid Quench) 18.4 (750C/162 hrs)				2179
$Al_{1-0}Nb_3Si_{0-1}$(Co-sputtered)	16-14-6		A15		▽2067
$Al_{0-0.1}Nb_3Sn_{1-0.9}$	17.8-18.0-17.9	HF			2374
$Al_xNb_3Sn_{1-x}$	∿16.6	HF			2108
$AlNb_{3-2.64}Ta_{0-0.36}$	18.6-14.5		A15		2323
$AlNb_{3-2.58}Ti_{0-0.42}$	18.6-9		A15		2323
$Al_{0-0.025}Nb_{0.33}Ti_{0.66}$	9.1-8.2	HF			2262
$AlNb_{3-0.55}V_{0-0.45}$	18.6-14		A15		2323
$AlNb_{3-2.85}W_{0-0.15}$	18.6-15.3		A15		2323
$AlNb_{3-0.85}Zr_{0-0.15}$	18.6-15.7		A15		2323
Al(O)(Implant, 10K,1300A)	4.0 Max.				▽2015

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Al_{\sim 0.75}Si_{0.25}$(Implant,500-1000A)	4-8.35				∇2296
$Al_{0.1-0.85}Si_{0.9-0.15}V_3$	11.5-12-10.5		A15		∇2069
$Al_{11}V$	≈1.5				2363
$Al_{10.6}V$	1.61-1.77(Annealed)			1.3 (Unannealed)	2363
$Al_{10}V$	1.7-1.6 0.99-1.06				2363
Al_7V	0.86,0.99				2363
Al_6V_1 Al_3V				1.3	2363
$Al_{0.25}V_{0.75}$(Liquid quench and various treatments				< 4.2	2245
$Al_{0-0.265}V_{1-0.735}$	5.43- < 0.5	HF	CUB		2320
$Al_{0.21-0.32}V_{0.79-0.68}$ (Co-sputtered at 530C)	8.8-9.7- < 2.5,11.7				∇2069
$AlV_{\sim 3}$(Sputtered, 600-850C, 3500-12,200A in Ar, Ne Kr and Xe)	11.8 - < 1.1				∇2025
$AlV_{\sim 3}$(Deposit 800C, in argon, 11,450A)	11.8-11.2		A15		∇2025
As_2B_{12}				2	2359#
$As_{0.99,0.96}Ge_{0.01,0.04}$				0.38	2330
$As_{0.04}Ge_{0.15}Te_{0.81}$	0.90-0.88	HF	RHOMB		2330
AsGeTe	0.43(750C/1 hr)				2330
$As_{0.39}Ge_{0.01}Te_{0.60}$				0.4	2330
$As_{0.04}Ge_{0.15}Te_{0.81}$(Amorphous)				0.05	2330
$As_{0.01}Ge_{0.49}Te_{0.50}$				0.4	2330
$As_{0.005}Ge_{0.005}Te_{0.99}$				0.4	2330
As_3La_4	0.65		CUB		2338
$As_{0-0.3}Mo_{1-0.7}$(Implant)	7.7- < 2				2382
$AsNb_3$	∼0.31	HF	TET		2237#
$As_{0.05}Te_{0.95}$				0.38	2330
As_2Te_3(P=100 k bar, ∼4000A)	4.4				∇2232

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Au					2070
$Au_{0.2}Cu_{0.2}Ge_{0.6}$(Deposit 12K, 3700A)	2.80- < 1.1				2263
$Au_{0.15}Cu_{0.10}La_{0.75}$	3.795 (Liquid quench)				2241
$Au_{1-0.90}Ga_{0-0.10}$	0.008-0.260				2401#
$Au_{0.97-0.90}Ga_{0.03-0.10}$	0.0078-0.264				2070
Au_2GaLa			B2	0.04	2006
Au_2GaSc			B2	0.04	2006
Au_2GaY			B2	0.04	2006
$Au_{0.20}Gd_{0-0.007}La_{0.80-0.793}$	3.6- < 1 (Amorphous)				2173
$Au_{0.975}Ge_{0.025}$	0.0141				2147
$Au_{0.057}H_{0.7-0.75}Pd$				1.4	2325
$Au_{0.94-0.90}In_{0.06-0.10}$	0.0114-0.0625				2070
Au_2InLa			B2	0.04	2006
Au_2InSc	3.02		B2		2006
Au_2InY	1.90		B2		2006
$Au_{0.24}La_{0.76}$(Liquid quench)	3.3 (Amorphous) 4.05 (Crystalline)	HF			2023
$Au_{0.22}La_{0.78}$(Liquid quench)	3.934 (Amorphous)				2241
AuLu	0.37				2006
$Au_{0.24-0.34}Mo_{0.76-0.66}$ (Implant)	2-2.7				2382
$AuNb_3$	10.5- ∿9		A15		2157
$Au_{0.24}Nb_{0.76}$	10.56		A15		2132#
$Au_{1-0}Nb_{2.33}Pt_{\sim 0-1}$	8.2-9.3-8.7 (Splat quenched) 9.2-10.1-8.2 (As cast) 10.7-11.5-6.7-6.3 (Annealed)		A15		2076
$Au_{1-0}Nb_4Pt_{\sim 0-1}$	8.4-9.4-5.7 (Splat quenched) 8.7-10.3-5.5 (As cast) 7.7-8.2-5 (Annealed)		A15		2076

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Au_xSb_{1-x}(Deposited 4.2K)	3.1 Max.				∇2072
AuSc	2.00		B2		2006
$Au_{0.96-0.95}Sn_{0.04-0.05}$	0.0184-0.047				2070
$AuTi_3$				0.015	2035#
$Au_{0.24}V_{0.76}$	2.97 (1100C...500C)				2132#
AuV_3	2.65		A15		1999#
AuV_3	$\lesssim$1.0		A15		1999#
AuV_3			A2	0.03	1999#
AuY			B2	0.04	2006
$Au_{0.80}Zn_{0.20}$	0.102				2147
$Au_{0.82}Zn_{0.18}$	0.093				2147
AuZn(P=0-23 K bar)	0.4-1.3-1.25		B2		2006
B(β)				2	2359#
B(P=0-100 K bar) ($B_{300-600}$Ca or Al or Si?)			CUB (a=23.32A)	0.04	2191
$B_xCr_{\sim0.85}Sc_{2.15}$	6.4		CUB		2111
B_4ErRh_4	8.7(Magnetic < 0.9K)		TET		2120 2316
$B_{0.072}H_{0.55-0.75}Pd$	< 1.4-3.5				2325
$B_{0.105-0.258}H_{0.7-0.4}Pd$	< 1.4-1.5				2325
B_2IrMo_2	3.60-3.45		ORTHO		2041
$B_2Ir_{1.2}V_{1.8}$	1.25		ORTHO		2041
B_2IrV_2	1.12		ORTHO		2041
B_4LuRh_4	11.76-11.54		TET		2316
$B_4Lu_{0.75}Rh_4Th_{0.25}$	11.93-11.3		TET		2316
$B_2Mo_{1.5}Ru_{1.5}$	3.72-3.60				2041
$B_2Mo_{1.75}Ru_{1.25}$	3.70-3.48		ORTHO		2041
$B_{0.5}Mo_5S_6Sn$	12.3				2161
$B_{0.047}N_{0.950}Nb_{0.949}O_{0.003}$	14.0		B1		2036
BNb			ORTHO	1.1	2041
B_4NdRh_4	5.36-5.26		TET		2316
B_2Os	2.1-1.98		ORTHO		2041

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
B_3Re_7	3.08-2.95		HEX		2041
$B_4Rh_4Sc_{0.75}Th_{0.25}$	8.74-8.49				2316
B_4Rh_4Sm	2.51-2.45		TET		2316
B_4Rh_4Th	4.34-4.29		TET		2316
B_4Rh_4Tm	9.86-9.73		TET		2316
B_4Rh_4Y	11.34-11.26		TET		2316
B_2Ru	1.60-1.57		ORTHO		2041
$B_{1.1}Ru$			HEX	1.1	2041
B_3Ru_7	3.38-3.32		HEX		2041
B_2RuMo_2	2.57-2.48				2041
$B_2Ru_{1.5}W_{1.5}$	3.28-2.83				2041
$B_2Ru_{1.25}W_{1.75}$	3.38-3.18		ORTHO		2041
B_2RuW_2	3.42-3.32				2041
$B_{66}Y$				2	2359#
$B_{61.7}Y$				2	2359#
$Ba_{0.9}Bi_{0.25}K_{0.1}O_3Pb_{0.75}$	11.73-11.32(P=0-14 kbar)				2149
$BaBiO_3$			ORTHO	4.2	2056
$BaBi_{0.05-0.3}O_3Pb_{0.95-0.7}$	∿9- ∿13				2056
$BaBi_{0.2}O_3Pb_{0.8}$	∿11				2056
Be (Deposited low temp., 60A)	8.6				∇2013
Be (Deposited low temp., 20-175A)	6.3-8.6-5.1				∇2013
$Be_{1-0}Bi_{0-1}$(Quench cond. < 5.6K, 180-700A)	9.0-4.1-6.1				∇2264
$Be_{1-0.68}Ga$ (Quench cond. < 5.2K, 250-620A)	8.7-6.4-8.4				∇2264
$Be_{1-0.68}Li_{0-0.32}$(Quench cond. < 6.1K, 260-410A)	8.8-1.7				∇2264
$Be_{1-0}Pb_0$(Quench cond. < 6.2K, 110, 450A)	9.0-5.2-7.2				∇2264
$Be_{0.031}V_{0.969}$(RRR=9.7)	4.86				2242#
Bi(III, IV, V)	6.8-7.2-7.1, 7.3-6.3 (P=30-38-47, 48-80 kbar)				2328
Bi (Deposited < 2K, 650-35A)	6-2.6				∇2307

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Bi_{1-0}Ga_{0-1}$(Deposited < 7.3K, 580-340A)	6.1-8.4				∇2264 ∇2073
$Bi_{0.01}H_{3.75}Th_{0.985}$	3.1		CUB		2159
$Bi_{0.22}In_{0.78}$	4.53, 5.61	HF			2243
$Bi_{0.006}In_{0.994}$(RRR=10, 18 micron spheres)	3.4949	284.1			2240
$Bi_{0.004}In_{0.996}$(RRR=14.6, 18 micron spheres)	3.4396	280.4			2240
$Bi_{0.0019}In_{0.9981}$(RRR=28.2, 18 micron spheres)	3.4051	277.9			2240
$Bi_{0-0.05}In_{1-0.95}$(Change Type I to II)	3.4-4.27	HF			2102
$Bi_{0-0.05}In_{1-0.95}$		HF			2355
Bi_3La_4	0.155		CUB		2338
Bi_2La_4Pb	2.3		CUB		2338
$BiLa_4Pb_2$	2.4		CUB		2338
$Bi_{1.5}La_4Sb_{1.5}$	0.158		CUB		2338
$Bi_{0-0.5}Pb_{1-0.5}$	7.3-7.8-8-9				2012
$Bi_{0-0.3}Pb_{1-0.7}$	7.2-8.65-7.9	HF			2110
$Bi_{0.1-0.35}Pb_{0.9-0.65}$(∿2000A)	7.65-8.95				∇2228
$Bi_{0-1}Pb_{1-0}$(Deposited < 6.1K, 800, 600A)	7.2-7.8, 6.85-7.0-6.15				∇2264
$Bi_{0.05,0.2}Pb_{0.9,0.6}Tl_{0.05,0.2}$ (2000A)	7.20, 7.26				∇2228
$Bi_{1-0.4}Sb_{0-0.6}$(Deposited ∿3K, < 3000A)	6-3				∇2051
$Bi_{0.97-0.8}Sb_{0.03-0.2}$ (II', III, IV, V, VI)	7.2-6.3 (P=30-80 kbar)				2328
$Bi_{0.80}Sb_{0.20}$(P=35-46, 49-63, 69-80 k bar)	6.3-6.4-6.2, 6.4-5.7, 5.7-5.3				2328
$Bi_{0.022}Sn_{0.978}$(Whiskers)	T_c'(0.20)(At 1.5% strain)				2235
Bi_2Te_3($p=2x10^{19}$)				1.5	2085

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Bi_2Te_3(p=2x10^{19})$	1.7-2.75-2.1 (I)(P=60-65-70 kbar) ∿3 (IV)(P=80-100 kbar)				2085
$Bi_2Te_3(n=9x10^{19})$	1.5-2.65-2.3 (I)(P=68-76-88 kbar) 2.7-2.9 (IV)(P=88-100 kbar)				2085
$Bi_2Te_3(p=1.5x10^{18})$	1.5-3 (I)(P=64-76 kbar) 4.3-3.9 (II)(P=71-85 kbar) 2.85 (IV)(P=80-100 kbar)				2085
$Bi_2Te_3(n=2x10^{18})$	1.5-2.2-1.75 (I)(P=75-80-90 kbar) 2.2-2.4 (IV)(P=88-100 kbar)				2085
$Bi_{0.1}Tl_{0.9}$(∿2000A)	2.30				∇2228
$Br_{0.4}NS$	0.25-0.32				2119
$C_{1.3-1.6}La$	11.1	HF	Data given		2219#
$C_{1-x}Mo$(Eta phase)	9.0				2094
$CMo_{0.05-0.85}Nb_{0.95-0.15}$	11.18-8.62 12.1-13.45-11.67 (1500C/30 min. at 120 kbar)		B1		2094
$C_{0.5-2}Mo_5S_6$	4.14-3.5				2161
CNNb (wires)					2078
$(C+N)_{0-1.6}Nb$	7.2- < 5-15-7		Data given		∇2321
$C_{0.14-0.27}N_{0.44-0.74}Nb$	Data given		Data given		2310
$C_{0.318}N_{0.662}Nb_{0.996}O_{0.001}$	16.4 (Considers vacancies)				2036
$C_{0-0.005}N_{-.921-0.807}Nb_{0.984-0.924}O_{0-0.23-0.094}$	13.3-12.2 (Considers vacancies)		B1		2036
$C_{0.03-0.98}N_{0.95-0}Nb_{0-0.01}O_{0-0.01}$	5.7-16.4 (Considers vacancies)		B1		2036
$C_{0.002-0.97}N_{0.937-0.004}Ta$	7.73-10.8 (Some pressure data)		B1		2144
$C_{0.89plus}Nb$(Implant)	3.7-11.3-4				2382
$C_{0.89}Nb$	3.7				2382
CNb(Fine powder)					2283
$C_{0.03}Nb_{0.56}Rh_{0.41}$	10.3 (1150C/24 hrs.)		CUB		2024
$C_{0.03}Rh_{0.43}Ta_{0.54}$	6.3-10				1997
$C_{0.98}Ta$	9.46		B1		2144
$C_{1.55}Th_{0.3}Y_{0.7}$	17.1	HF	CUB		2188
$C_{0.88plus}V$(Implant)	3.2				2382
$C_{0.66}Zr_{0.34}$	1.35, 0.93, 0.8				2082
$C_{0.365}Zr_{0.635}$	4......0.75		B1		2082
$C_{0.39-0.495}Zr_{0.61-0.505}$			B1	0.3	2082

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$C_{0.111}Zr_{0.889}$				0.3	2082
Ca_xMoS_2	4.0	HF			2273
Cd(99.9999)	0.503 (Single crystal)				2251
Cd(99.999)	0.52				2236
Cd(Whiskers, 4 orientations)	0.506-0.484 (Also at 0.7% strain, also at $3x10^8 N/m^2$)				2236
$Cd_{0.945}Cu_{0.055}Mn_{0-0.004}$ (Quench cond.)	1.15- < 0.070				▽2392
$Cd_{1-0.999}Mn_{0-0.001}$ (Quench cond.)	0.9-0.5				▽2392
$CdMn_{0-20}$ ppm atomic	0.5- < 0.02				2134
$Cd_{0.002}Sn_{0.998}$(whisker)	T_c'(0.20)(At 0.5% strain)				2235
Ce(RRR=∿80)	0.020-0.045(P=20-35 kbar)		A1		2362
Ce	1.9-1.3(P=45-125 kbar)				2362
$Ce_{0.1}H_{3.75}Th_{0.9}$			CUB	1.8	2159
$Ce_{0.01}H_{3.75}Th_{0.99}$	5.6		CUB		2159
$Ce_{0-0.025}In_{1-0.975}$	4.4- < 1.3				2213
$Ce_{0.008}La_{0.992}$	4.84		Data given		2400#
$Ce_{0-0.017}La_{1-0.983}$	4.61-2.37		Data given		2400#
$Ce_{0.2}La_{0.8}Mo_6Se_8$	8.9	HF	RHOMB		2196
$Ce_{0-0.01}La_{1-0.99}Pb_{3.0}$	4.18- < 1.5				2212
$Ce_{0-0.1}La_{1-0.9}Sn_{3.0}$	6.45- < 1.5				2212 2297
$Ce_{0.0075}La_{0.80}Th_{0.20}$(Re-entrant)	5.25- < 0.045	HF	CUB		2167
$Ce_{0.0075}La_{0.80}Th_{0.20}$	∿1.3 (Magnetic at < 0.045K)	HF	CUB		2167
$Ce_{0.004}La_{0.80}Th_{0.20}$	3.6	HF	CUB		2167
$Ce_{0-0.0077}La_{0.90}Th_{0.10}$	5.41-3.03				2400#
$Ce_{0-0.006}La_{0.75}Th_{0.25}$	4.82-1.45				2400#
$Ce_{0.004}La_{0.55}Th_{0.45}$	3.85-1.45				2400#
$Ce_{0-0.003}La_{0.35}Th_{0.65}$	2.48-1.26				2400#
$Ce_{0-0.0055}La_{0.2}Th_{0.80}$	1.83-1.00				2400#

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Ce_xLa_{3-x}Y$		HF			2360
$Ce_2Mo_6S_8$				0.6	2161
$CeMo_6S_8$			HEX	1.1	2050
$Ce_{0-0.06}Pb_{1-0.94}$	6.7- < 1.3				2213
$Ce_{1-0.6}Pr_{0-0.4}Ru_2$	6.20-6.55- < 1.5		C15		2292#
$CeRu_2$	6.28	HF	C15		2096
$CeRu_2$	6.20		C15		2292#
$Ce_{0-0.10}Sc_{0.2}Th_{0.8}$	1.75-0.07				2334
$Ce_{0-0.09}Th_{1-0.91}$	1.36-0.05				2334
$Ce_{0.007}Th_{0.993}$	1.09				2400#
$Ce_{0-0.04}Th_{0.8}Y_{0.2}$	1.65-0.07				2334
$Ce_{0-0.015}Th_{0.65}Y_{0.35}$	1.45-0.06				2334
$Ce_{0-0.002}Th_{0.44}Y_{0.56}$	0.65-0.11				2334
$Ce_{0-0.105}Th_{0.9}Zr_{0.1}$	1.93-0.2				2334
$Co_{0.075}NbSe_2$	4.5	HF			2225
$Co_{0-0.09}NbSe_2$	7-1-4.2- < 1		HEX		2210
$Co_{0-0.07}Nb_3Sn$	$^{Tc}/Tco$ =1-0.98		A15		2322
$Co_{0-0.059}Tc_{1-0.941}$	7.85-5.98				2337
$Co_{0-0.02}Ti_{1-0.98}$					2256
Cr (Evap. films on carbon)			A15	0.5	$^{\nabla}$2205
$Cr_{0-3}GaV_{3-0}$	13.5-5.5		A15		2011
$Cr_{0-0.09}Nb_{1-0.91}$(Weight fractions)	9.2-5.4-9.4				2052
Cr_xNb_3Sn	T_c'(-1.6-0.9)				2052
$Cr_{0-0.044}Tc_{1-0.956}$	7.85-6.60				2337
$Cr_{0-0.04}Ti_{1-0.96}$					2256
$Cs_{0.1}F_{0.1}O_{2.9}W$	4.87-4.94	HF	HEX		2046
$Cs_{0.3}MoS_2$	6.9	HF			2273
$Cs_2Mo_6S_8$				0.6	2161
Cu					2070
$Cu_{0.86-0.81}Ga_{0.14-0.19}$	0.0074-0.048				2070

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Cu_{0.036}Ga_{0.25}Nb_{0.71}$	6-8 (Liquid quenched)				2245
$Cu_{0.20}Ga_{0.18}V_{0.62}$(Liquid quenched)				4.2	2245
$Cu_{0.90}Ge_{0.10}$	0.0177		CUB		2147
$Cu_{0.3-0.7}Ge$(Implant, ∿2500A)	1.8-3.2-1.9				∇2365
$Cu_{0.26}Ge_{0.74}Kr_x$(Implant, ∿2500A)	1.4-3.3				∇2365
$Cu_{0.158-0.359}H_{0.85-0.55}Pd$	< 1.4-6.3				2325
$Cu_{0.081}H_{0.65-0.85}Pd$	3-8.7				2325
$Cu_xKr_yTe_{1-x}$(Implant)(Quench condensed)				0.37	∇2365
CuLu			B2	0.04	2006
$Cu_{0.1}Mn_{0-0.003}Pb_{0.9-0.897}$ (Deposited < 3K, ∿500A)	6.5- < 0.3				∇2364
$Cu_{1.7}Mo_3S_4$(P=0-22 kbar)	4.5-6.2-7				2128
$Cu_{1.2}Mo_3S_4$(P=0-22 kbar)	10.6-11.5-10.4				2128
$Cu_{1-1.9}Mo_3S_4$	10.9-10.5, 6.5-5.8, 4.6-4.1				2128
$Cu_2Mo_6S_8$	10.4	HF	RHOMB		2408
$CuMo_3S_4$	10.6, 10.4	HF	RHOMB		2408
$Cu_{0.7}Mo_3Se_4$	5.8, 5.9	HF			2408 2287
$Cu_{1.3}Mo_3Se_4$	4.6		RHOMB		2408
$Cu_{0.40-0.56}Nb_{0.35-0.19}Sn_{\sim 0.25}$ (Deposited 900C, 3000-10,000A)	17.5-18.1				∇2265
$Cu_{0-0.03}Nb_{0.33}Ti_{0.66}$	9.3-8.8-9.2	HF			2262
$Cu_{0.97-0.84}Pb_{0.03-0.16}$ (Weight Fraction)	7.2-0.3				2157
$CuRh_2S_4$	3.81, 4.70, 4.76, 4.7-5.8, 3.8-4.4 (P=0-22 kbar)		$H1_1$		2148
$CuRh_2Se_4$	3.38-3.7(P=0-22 kbar)		$H1_1$		2148
$Cu_{0.2-0.8}Sb_{0.8-0.2}$ (Deposited 4.2K, 600-1700A)	1.5-2.5-1.4				∇2072
CuSc			B2	0.04	2006

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Cu_{0.905}Si_{0.095}$	0.0129		CUB		2147
$Cu_{0.90}Si_{0.10}$	0.0206		CUB		2147
$Cu_{15}Si_4$			CUB	1.5	2155
$Cu_{0.38}Si_{0.62}Kr_x$(Implant, quench cond.)	1.02				∇2365
$Cu_{0.103-0.182}Sn_{0.90-0.82}$ (590-1700A)	6.29-6.57				∇2077
CuY	0.47		B2		2006
$D_{0-1}HfV_2$	9.7-3.4	HF			2122
$D_{0-1}HfV_2$	9.7-3.3		C15		2339
$D_{0.5}HfV_2$	5.8	HF	C15		2339
$D_{0.97-0.72}Pd$	8.2-1.3				2229
$D_{0.87-0.91}Pd$	3.8-3.5-5.4				2324#
$D_xPd_{1-0.85}Rh_{0-0.15}$(Implant)	10-3.5				2347
$D_{15}Th_4$	8.42		CUB		2155
$D_{15}Th_4$	8.00				2239#
$D_{15}Th_4$	7.9				2353
Dy_xLaSn_3	T_c'(-)				2297
$Dy_2Mo_6S_8$	2.1				2161
$Dy_{1.2}Mo_6Se_8$	5.77-5.30		HEX		2050
Er_xLaSn_3	T_c'(-)				2297
$Er_2Mo_6S_8$	2.19				2161
$Er_{1.2}Mo_6Se_8$	6.17-5.70, 1.9		HEX		2050
$Eu_{0-0.007}La_{1-0.993}$	5.12-3.5		HEX		2127
$Eu_{0-0.012}La_{1-0.987}$	4.7- <0.6 (Ferromagnetic <∿0.8K)				2168
$Eu_{0.2}La_{0.8}Mo_6Se_8$	10.7-11.4	HF	RHOMB		2196
$EuMo_6S_8$			RHOMB	1.1	2008
$Eu_{0.67}Mo_6S_8Sn_{0.33}$	8		RHOMB		2008
$Eu_{0.5}Mo_6S_8Sn_{0.5}$	13.0				2121
$Eu_{0.33}Mo_6S_8Sn_{0.67}$	10.6		RHOMB		2008
$Eu_{0.1-0.8}Mo_{6.35}S_8Sn_{1.1-0.24}$	11.5	HF			2408
$Eu_{1.2}Mo_6Se_8$			HEX	1.1	2050
$EuSm_xSn_3$	T_c'(-)				2297

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Fe_{0-0.8}GaV_{3-2.2}$	13.5-2		A15		2011
$Fe_{0.3}HfV_{1.7}$	5	HF	C14		2081
$Fe_{0.15}HfV_{1.85}$	9.5	HF	C14		2081
$Fe_{0-0.3}HfV_{2-1.7}$	9.3-5				2081
$Fe_{0-0.07}Nb_{0.72-0.81}Pt_{0.28-0.19}$	8.56- < 0.5		CUB		2398
$Fe_{0-0.05}Nb_{0.76}Pt_{0.24-0.19}$	8.56-1.80(Disordered) 10.10-1.40(Ordered)	HF			2398
$Fe_{0-0.04}Nb_{0.76}Pt_{0.24-0.19}$		HF			2398
$Fe_{0-0.0125}NbSe_2$	7- < 1		HEX		2210
$Fe_{0.05}NbSe_2$				∿1.5	2042
$Fe_{0.034}Nb_3Sn$	17	HF	A15		2322
$Fe_{0.017}Nb_3Sn$	17.5	HF	A15		2322
$Fe_{0-0.07}Nb_3Sn$	$^{Tc}/Tco$=1-0.96-0.91		A15		2322
$Fe_{0.05}S_2Ta_{0.95}$	3.2-2.7	HF			2042
$Fe_{0-0.10}S_2Ta$	0.8-3.3- < 1.3	HF			2225
$Fe_{0-0.06}SiV_3$	$^{Tc}/Tco$=1-0.88		A15		2322
$Fe_{0-0.037}Tc_{1-0.963}$	7.85-4.9				2337
$Fe_{0.025}Ti_{0.975}$	$3.1_5-3.6_5$				2256
$Fe_{0.98}U_6$(Neutron irradiation)	3.92- < 2.08				2300
$Fe_{0.3}V_{1.7}Zr$	4.4	HF	C15		2081
$Fe_{0-0.3}V_{2-1.7}Zr$	8.8-4.2				2081
Ga (Alpha)		58.3			2022
Ga (Deposited < 2K, 400-35A)	8.3-4.2				∇2307
$Ga_{0-1}Ge_{1-0}Nb_3$(Co-sputtered)	16-13-14.5		A15		∇2067
$GaHf_{0.015}V_{0.985}$					2254
$Ga_{0.05-0.345}Ir_{0.02-0.15}Nb_{0.625-0.835}$	16- < 4.2				2158
$Ga_xIr_yNb_{0.625-0.80}$			$D8_b$	4.2	2158
$GaMn_{0-1.2}V_{3-1.8}$	13.5-2		A15		2011
$Ga_{0.5}Mo_5S_6Sn$		HF			2089
$Ga_{0.5}Mo_5S_6Sn$(P=0-100 kbar)	13.5-4	HF			2317

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Ga_{0.5}Mo_5S_6Sn$	14.2		Data given		2307
$GaNb_3$	20.7		A15		2125
$Ga_{0.20-0.25}Nb_{0.80-0.75}$	7-20.7(650C/1 mon.) 7-18(Argon quenched)				2125 2166
$GaNb_3$	16.0		A15		2158 2180 2295
$GaNb_3$(Neutron irradiation					2190
$Ga_{0.16-0.35}Nb_{0.84-0.65}$	10.4-15.9-14.1(As cast) 6.0-14.8-7.8(Liquid quenched)				2245
GaNb	17.3 from 16.3(Laser beam quenched)				2106
$GaNb_3$	16.8				2299
Ga_4Nb_5(With $Ir_{0.005}$)				4.2	2158
$Ga_{0.08-0.35}Nb_{0.92-0.65}$ (Deposited 50C-750C)	17.3-5		A15		▽2370
$Ga_{\sim 0.23-0.35}Nb_{0.77-0.65}$ (Sputtered)	∿13-∿16-15		A15		▽2067
$Ga_{0.85-0.1}Nb_3P_{0.15-0.9}$	12-5.5(Co-sputtered)				▽2067
$Ga_{1-0}Nb_3Si_{0-1}$(Co-sputtered)	13.5-6		A15		▽2067
$Ga_{0.01-0.04}Nb_{0.73-0.82}Sn_{0.26-0.14}$	17.8-18.1-18.0	HF			2374
$Ga_{0-1}Pb_{1-0}$(Deposited < 7K, 750-575A)	7.2-6.8-8.4				▽2264
$Ga_{0.40}Re_{0.60}$	2.8		HEX		2207
$Ga_{0.028}Re_{0.972}$	3.02		HEX		2207
$Ga_{0.205}Re_{0.795}$	2.655		HEX		2207
$Ga_{0.20}Re_{0.80}$	2.7		HEX		2207
$Ga_{0.16}Re_{0.84}$	2.9		HEX		2207
$Ga_{\sim 0.05}Re_{0.95}$	2.9		HEX		2207
$Ga_{0.5}Sn_{0.5}V_3$	5.6				2272#
GaV_3	14.3				2272#
GaV_3	14.02-14.82				2254
GaV_3	15.1				2138#
GaV_3	13.8, 13.5				2138#
GaV_3	15.85, 13.6		A15		2125

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Ga_{0.248}V_{0.752}$	15.7-14.3(Order from 0.95-0.84)		A15		2343
GaV_3(Irradiation)		HF			2381
$Ga_{0.205-0.318}V_{0.795-0.682}$	9.53-15.26-5.61 (1400C/4 hrs.)		A15		2280
$Ga_{0.219-0.282}V_{0.781-0.718}$	13.25-14.56-9.69 (Above plus 1150C/ 7 hrs.)		A15		2280
$Ga_{0.15-0.36}V_{0.85-0.64}$	8.0-14.8-7.0(As cast) < 4.2-<< 13.9- < 4.2 (Liquid quench)				2245
$Ga_{0-0.12}V_{1-0.88}$	5.1-1.6		CUB		2266
$GaV_{0.97}Zr_{0.03}$					2254
$Gd_{0-0.005}La_{1-0.995}Pb_{3.0}$	4.18- $\gtrsim$ 4.2				2212
Gd_xLaSn_3	T_c' (-)				2297
$Gd_{0-0.055}La_{1-0.945}Sn_3$	6.43, 6.39-4.79				2358
$Gd_{0.01-0.055}La_{0.99-0.945}Sn_3$ (P=0-18, 19 kbar)	T_c'(-0.015, -0.075, -0.21)				2358
$Gd_{0.4}Mo_{6.35}Pb_{0.6}S_8$	4.9	HF	RHOMB		2408
$Gd_{0.6}Mo_{6.35}Pb_{0.4}S_8$	3.0	HF	RHOMB		2408
$Gd_{0-0.6}Mo_{6.35}Pb_{1-0.4}S_8$	12-14-2.8		RHOMB		2408
$Gd_2Mo_6S_8$	2.2				2161
$Gd_{0-0.6}Mo_{6.35}S_8Sn_{1.2-0.6}$	10.3-12.5-6.7		RHOMB		2408
$Gd_{0.6}Mo_{6.35}S_8Sn_{0.6}$	6.7	HF	RHOMB		2408
$Gd_{1.2}Mo_6Se_8$	5.59-5.24		HEX		2050
$Gd_{1.2}Mo_6Se_8$	5.6		RHOMB		2287
$Gd_{0.00125-0.09}Nb_{0.999-0.91}$ (Implant, 400A)	T_c' (-3.8, 2, 1.3)				∇2233
$Gd_{0-0.25}Nb_{\sim0.5}Sn_{0.5-0.25}$ (Deposited 900C, 3000-10,000A)	18-16.5-18-15, 16-14.5				∇2265
$Gd_{0-0.11}Ru_2Th_{1-0.89}$	3.3-3.4-2.3				2288
$Gd_{0.0015}Th$	0.9	85			2336
$GeMo_{0.09-0.39}Nb_{2.91-2.61}$ (Deposited 700-900C)	18-12-13-11				∇2282
$GeNb_{2.6}$(Deposited 720C, ∿2000A)	23.2-21.9		A15		∇2214

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$GeNb_3$(Deposited ∿975C, ∿4000A)	23.0-20.85		A15		▽2184 ▽2380 ▽2118 ▽2221 ▽2117 ▽2306 ▽2115 2180 ▽2284 2166
$GeNb_{5.52-1.96}$(Deposited 720-800C, 2000-3500A)	9.6-23.2-12.8-19.6				▽2214
$Ge_{0.1-0.17}Nb_{0.9-0.83}$(50-4000A)	∿9-22		A15		▽2112
$Ge_{0.16-0.3}Nb_{0.84-0.7}$ (On Nb_3Ir films)	8-21.5-18.5		A15		▽2410
$GeNb_3$(Co-sputtered films)	23- <1.4		A15		▽2395 ▽2309 ▽2060 ▽2067 ▽2017 ▽2290 ▽2284 ▽2372 ▽2007 ▽2367
$GeNb_3$("Round Robin," Sputtered, Al_2O_3, ∿930C)	22.7-17.7 19.7-18.4				▽2194 ▽2376
$GeNb_3$(Irradiated, helium ions) (Neutrons)	22-3.5 20.6- <1.5 (Recovers 900C)		A15		▽2372 ▽2044 ▽2060 ▽2397 ▽2190
$GeNb_3$(Chem. vapor. deposition 750-900-1000C)	21.7, 21.2	HF	A15		2341 2018 2397 2260# 2367
$GeNb_3$(P of 70-90 kbar, 2000C, 15-30 sec.)	22.2-19.7		A15		2315
$Ge_{0.16-0.29}Nb_{0.84-0.71}$	5.7-6.9-5.8-6.0-5.9(As cast) 5.3-5.7-6.1(Liquid quenched)				2245
$GeNb_3$(Laser heated)	17.3 from ∿14				2106
$GeNb_3$(Granular)	10.3-7.5	HF			▽2345

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$GeNb_3$(Amorphous, RF sputtered)	3.342				2241
Ge_2Nb				2.5	2115
$GeNb_3O_x$(Deposited 950-1050C)	20.5-19.5		A15		∇2368
$Ge_{1-x}Nb_3O_x$(RRR=1.1-2.6)	21.5				∇2153
$GeNbO_x$(Low oxygen)	10-13				2182
$GeNb_3(O_2Cl)$(Deposited 875-600C)	21.5				∇2369
GeNb(Plus 0.05 O,C,N)(Implant 2000-4000A)	15-21.6				∇2060
$GeNb_3O_x$(Various O_2 pressures)	15-21-20				2182
$Ge_{0.85-0.9}Nb_3P_{0.15-0.9}$ (Co-sputtered films)	6-5-5.8-4.5				∇2067
$Ge_{1-0}Nb_3Si_{0-1}$(Co-sputtered films)	16.5-12.5-11.5-6				∇2067
$Ge_{0-0.02}Nb_{0.33}Ti_{0.66}$	8.9-8.2	HF			2262
$Ge_{0.04,0.01}Sb_{0.96,0.99}$				0.38	2330
$Ge_{0.45}Te_{0.55}$	0.51	HF			2330
$Ge_{0.05}Te_{0.95}$	0.40	HF			2330
$Ge_{0.01}Te_{0.99}$	0.41(850C/2 hr. slow cool)	HF			2330
$Ge_{0.55}Te_{0.45}$			RHOMB	0.38	2330
$Ge_{0.01}Te_{0.99}$	(Water quench)			0.45	2330
$Ge_{0.001}Te_{0.999}$				0.4,0.45	2330
$Ge_{0.20-0.30}V_{0.80-0.70}$	5.8-6.1-6.0 6.0-6.5-5.4-5.9(Liquid quench)				2245
$GeV_{\sim 3}$(Sputtered on hot surface, ∼2500-4000A)	7-6				∇2221
GeV_3(Irradiated, helium ions)	7-1.0				∇2372 ∇2118 ∇2221
$H_{0-1.6}HfV_2$	9.7-22	HF	C15		2122 2339
$H_{15}La_{0.048}Th_{3.952}$	5.9		CUB		2155
$H_{3.75}La_{0.01}Th_{0.99}$	5.2		CUB		2159
$H_{3.7-3.0}La_{0.1-0.99}Th_{0.9-0.01}$				1.8	2159
$H_{15}Lu_{0.048}Th_{3.952}$	6.2		CUB		2155
$H_{0.51}Mo_{0.1}Nb_{0.765}Pd_{0.135}$	5.56-4.90				2257

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$H_{0-0.46}Mo_{0-0.1}Nb_{0.765-0.61}Pd_{0.15-0.24}$	5.46- < 1.2		Data given		2257
H_2Nb				1.2	2156
$H_{0.39}Nb_{0.8}Pd_{0.2}$	2.7-2.5		CUB		2071
$H_{0-0.74}Nb_{0.80}Pd_{0.20}$	1.52- < 1.3-4.07				2257
$H_{0.12-0.75}Nb_{0.85-0.65}Pd_{0.15-0.35}$	4.66- < 1.3				2257
$H_{0.47}Nb_{0.72}Pd_{0.18}W_{0.1}$	3.99-2.54				2257
$H_{0.10}Nb_{0.8}Rh_{0.2}$	5.96-5.64		B2		2071
$H_{0.51}Nb_{0.80}Ru_{0.20}$	5.52-5.36-5.21		CUB		2061
$H_{0.35}Nb_{0.75}Ru_{0.25}$	4.97-4.78-4.64				2061
$H_{0.21}Nb_{0.67}Ru_{0.33}$	$\approx$2.0				2061
$H_{0.11}Nb_{0.80}Ru_{0.20}$				0.9	2061
H_xNb_3Sn			A15		2180
$H_xNi_{0.07}Pd_{0.93}$	1.7				2347
HPd	9.62	HF			2349
$H_{1-0.933}Pd$	9.62-5.5	HF			2349
$H_{0.99-0.82}Pd$	7.3-1.3				2229
$H_{0.78-0.96}Pd$	< 3.2-6.2				2080#
$H_{\sim0.82-0.88}Pd$	1.7-3.1 1.43-2.43(Calorimetric)				2034#
$H_{0.65}Pd$				1.8	2033
$H_{0.225}Pd$				1.8	2033
$H_{0.88-0.94}Pd$($\sim$2000A)	2-6.8				∇2350 ∇2058 ∇2198 ∇2348
$H_xPd_{0.8}Pt_{0.2}$(Implant)	9				2347
$H_xPd_{1-0.4}Pt_{0.06}$(Implant)	8.7-9- < 1				2347
$H_{0.72-0.82}PdRh_{0.06}$	2.5-4.2				2304#
$H_xPd_{1-0.85}Rh_{0-0.15}$(Implant)	9-2.5				2347
$H_4Pd_5Th_3$				1.8	2033
H_4PdTh				1.8	2033
H_6PdTh_2				1.8	2033
$H_{15}Sc_{0.048}Th_{3.952}$	6.4		CUB		2155

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
HTa				1.2	2156
$H_{15}Th_4$	8.5,7.97,7.9,7.5				2156 2353# 2239# 2159
$H_{15}Th_4$	8.8,7.5		(Two Modifications)		2155
$H_{15}Th_4$			1.8		2033
H_2Th			1.2		2033 2156
$H_{15}Th_{0.048}Y_{3.952}$	7.25		CUB		2155
$H_{3.75}Th_{0.99}Y_{0.01}$	3.5		CUB		2159
$H_{3.7}Th_{0.95}Y_{0.05}$			CUB	1.8	2159
$H_{15}Th_{3.84}Zr_{0.16}$	6.6		CUB		2155
$H_{3.75}Th_{0.99}Zr_{0.01}$	4.9		CUB		2159
H_7ThZr_2				1.2	2156
$H_{3.5,3.0}Th_{0.9,0.5}Zr_{0.1,0.5}$			CUB	1.8	2159
H_2V				1.2	2156
Hf	0.128	12.7			1996#
$Hf_{0.65}Nb_{0.35}$	6.5-7.5 6.5-6.4				2286
$Hf_{0.063-0.657}Nb_{0.94-0.34}$	9.76-9.81-6.18				2074#
$Hf_{0.26}Nb_{0.74}$	9.3	HF			2222#
$Hf_{0-0.05}Nb_{1-0.95}$(Weight fractions)	9.2-9.4				2052
Hf_xNb_3Sn	T_c'(-0.8)				2052
$Hf_{0.30}Ta_{0.70}$			A2	2404#	
$Hf_{0-0.07}Th_{1-0.93}$	1.36-1.7				2334
HfV_2	9.7,9.3,8.4	HF	C15		2312# 2081 2339 2005#
HfV_2(Irradiated 6K, Fast neutrons)	9.22-8.8		C15		2285
$Hf_{0.15-0.6}V_{0.85-0.4}$	9-9.3-8.4	HF			2005
$Hf_{0.009}V_{0.991}$(RRR=29.5)	5.34				2319#
$Hf_{0.55}V_2Zr_{0.45}$		HF			2005
$Hf_{0.5}V_{2.3}Zr_{0.5}$	10.1				2005

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Hf_{0.5}V_2Zr_{0.5}$	10.1	HF			2005#
$Hf_{0.4-0.3}VZr_{0.6-0.7}$	10.2	HF	C15		2183
$Hf_{0-1}V_2Zr_{1-0}$	8.5-10.1-9.2	HF	C15		2005
Hf_xVyZr_{1-x-y}	10.1-7.8	HF			2005
Hg(Deposited 2.3K, >1000-100-70A)	3.87-4.08-4.05				▽2090
Hg(64.5-92A)	4.07-4.05-4.5 (0 to 80K anneals)				▽2090
Hg(300-10,880A)	T_c'(∿-0.2)	HF			▽2091
Hg(23A pores in asbestos)	3-5				2327
$Hg_{0.007}In_xTl$	T_c'(-0.14+0.22)				2101
$Hg_xIn_{0.02}Tl$	T_c'(0+0.12-0.01)				2101
$Hg_xIn_{0.01}Tl$	T_c'(+0.5-0.1)				2101
$Hg_{0.007}Sb_xTl$	T_c'(-0.014+0.14)				2101
$Hg_xSb_{0.0008}Tl$	T_c'(-0.001-0-0.012)				2101
Hg_xTl_{1-x}	T_c'(-0.14)				2101
Hg_xTl	T_c'(-0.014) Also P to 12 kbar				2101
Ho_xLaSn_3	T_c'(-)				2297
$Ho_{1.2}Mo_6Se_8$	6.10-5.54		HEX		2050
In					2394
In(RRR>16,000g 18 micron spheres)	3.4089	278.2			2240
In(Particles, 100A)	3.9				2064
In(290-20,000A)	3.52-3.39(From intermediate to mixed state at ∿6000A)				▽2066
In(TypeI to Type II)	Data given	Data given			▽2065
In(Multilayered films)	3.6-5.6				▽2000
In(On PbTe, 15-340A)	2.2-∿5.5	HF			▽2250
In(In)(Implant at 2K)	3.65-4.4 4.26-4.54				▽2195
In_3La			$L1_2$	1.0	2274
$In_{0.98-0.874}Mg_{0.02-0.126}$		HF			2104
$InMn_{0.0003}$(Deposited 4.2K, 3900A)	2.51				▽2247

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$InMn_{0-700ppm}$(Implant 2K)	3.5-1.4 3.7-2 (With In ion implant)				2171
$In_{0.01-0.04}Nb_{0.78-0.73}Sn_{0.21-0.23}$	17.8-18.1	HF			2374
$In_{0.9-0.2}Pb_{0.1-0.8}$	4.6-6,6.6-7				2012
$In_{0.17}Pb_{0.83}$		HF			2375
$In_{0.013-0.10}Pb_{0.987-0.90}$		HF			2103
$In_{1-0.933}Pb_{0-0.067}$(Whiskers)	T_c'(0.015)(0.2% strain) T_c'(0.012)(0.46% strain) T_c'(-0.004+0.002)(0.6% strain)				2235
$In_{1-0.93}Sn_{0-0.07}$	3.4-3.4-4.1				2356 2394
$In_{1-0}Sn_{0-1}$					∇2223
$InSn_4$	4.54	HF	HEX		2326
$In_{1-0.921}Sn_{0-0.079}$	T_c'(0.017)(At 0.25% strain) T_c'(-0.003-0.002)(At 0.32% strain)				2235
$In_{0.06}Sn_{0.94}$	T_c'(0.34)(At 2% strain)				2235
In_xTl_{1-x}	T_c'(+0.4)(Also P to 12 kbar)				2101
InTl(190A, 90A)	4.145, 3.880	HF			∇2211
InTl(300A, 180A)	2.910, 3.530	HF			∇2211
$InTl_{0-0.048}$ (Whiskers)	T_c'(To+0.18)(0.25% strain)				2235
$In_{0.94}Zn_{0.06}$(Implant)	3.65-4.3				∇2195
$Ir_{0.42}Nb_{0.58}$	4-9(As cast) 7-9(Quenched)		Data given		1997
$IrNb_3$	1.66		A15		2132#
$Ir_{0.22-0.29}Nb_{0.78-0.71}$			A15	4.2	2158
$Ir_{0.455}Nb_{0.455}O_{0.09}$	8-9.2				1997
$Ir_{0.40}Nb_{0.55}O_{0.05}$	10.5, 11.7		TET		1997
$Ir_xOs_yTi_{1-x-y}$	4.2-4				2035
$Ir_{0.25-0}Pt_{0-0.25}Ti_{0.75}$	4.2-5.6-0.6				2035#
$Ir_{0.2}Pt_{0.05}Ti_{0.75}$	5.53				2035#
$Ir_{\sim 0.45}Ta_{0.55}$(Evaporated, ∿1000A)	2				2126
$Ir_{0.42}Ta_{0.58}$(Liquid quenched)	6.6		Data given		1997
$IrTi_3$	4.3				2035#

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Ir_{0.18-0.32}Ti_{0.82-0.68}$	3.7-5-4.5		Data given		2035
$Ir_{0.05-0.18}Ti_{0.95-0.82}$	2.7-4- < 1		Data given		2035
$Ir_{0.38}V_{0.62}$	1.94	HF			2175
Ir_3Zr				1.85	2269
Ir_2Zr	4.03				2269
IrZr	2.3 2.1 (As cast)			1.85	2269
$Ir_{0.375}Zr_{0.625}$				1.85	2269
$IrZr_3$	2.55, 7.05 2.1				2269
$Ir_{0.3}Zr_{0.7}$	2.5, 7.35 7.3				2269
$IrZr_2$	2.75, 7.35 7.3				2269
$Ir_{0.2}Zr_{0.8}$	4.3 3.15, 6.2				2269
$Ir_{0.1}Zr_{0.9}$	5.5 3.5, 3.9, 4.35, 2.1				2269
$K_{0.4}MoS_2$	6.9	HF			2273
$K_2Mo_6S_8$	2.7				2161
$Kr_{0-0.043}Nb_{1-0.957}$(2000A)	9.8-9.3-9.4		CUB		▽2281
La	5.99		87% CUB		2400
La	5.12		HEX		2127 2400
La(P=0-25 kbar)	4.8-7.5		HEX		2354
La(P=0-25-53-210 kbar)	5.9-8.7-10-12.9		CUB		2354
La(Deposited $\approx$150K, 5000-10,000A)	4.90	HF			▽2145
$La_{0.92}Lu_{0.08}$	3.72				2068
$LaLu_xSn_3$	T_c'(-)				2297
$La_{0.2}Mo_{6.35}Pb_{0.8}S_8$	13.2	HF	RHOMB		2408
$La_{0-0.6}Mo_{6.35}Pb_{1-0.4}S_8$	12-13.4-5		RHOMB		2408
$La_{0.5}Mo_5S_6Sn$	12.2-11.4				2161
$La_{1.0}Mo_6Se_8$	11.39-11.05		HEX		2050

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$LaMo_6Se_8$	11.3	HF	RHOMB		2196
$La_{0.98}Nd_{0.02}$	3.60				2068
$LaNd_xSn_3$	T_c'(-)				2297
$LaOs_2$	9	HF	C15		2096
$LaPb_3$	4.05		$L1_2$		2274
$LaPb_{0-3}Tl_{3-0}$	1.7-0.5-2.2-0.1-4.5-4.2 (Also P study)				2059
$La_{0.84}Pr_{0.16}$	2.20				2068
$LaPr_xSn_3$	T_c'(-)				2297
$La_{1-0.958}Pr_{0-0.042}Sn_3$	6.5-1.3	670-180			2357#
$La_{1-0.97}Pr_{0-0.03}Sn_3$	6.43-2.33				2358
$La_{0.99-0.97}Pr_{0.01-0.03}Sn_3$ (P=0-18 kbar)	T_c'(-0.30, -0.24, -0.26)				2358
$LaRu_2$	4.45		C15		2403#
La_3S_4	8.12-11.5(P=0-22 kbar) ∿6-∿5(P=10-150 kbar, non-hydrostatic)				2040
La_4Sb_3	0.25		CUB		2338
La_3Sb_3Y	0.13		CUB		2338
La_3Se_4(n=1.20-3.67x10^{21})	2.60-6.86	HF			2079#
La_3Se_4	7.63-9.4-8.7(P=0-22 kbar) ∿4.5-3(P=30-160 kbar, non-hydrostatic)				2040
$La_{1-0.987}Sm_{0-0.013}Sn_3$	6.38-0.3		$L1_2$		2154#
$LaSm_xSn_3$	T_c'(-)				2297
$LaSm_3Tb_x$	T_c'(-)				2297
$LaSn_3$	6.54, 6.628, 6.45		$L1_2$		2057 2274 2297
$LaSn_3$(P=0-7-22 kbar)	T_c'(0-+0.02-0.045)		CUB		2054
$LaSn_3$(P=0-19 kbar)	T_c'(-0.10)				2358
$LaSn_3Tm_x$	T_c'(-)				2297
$LaSn_3Yb_x$	T_c'(-)				2297
La_3Te_4(P=0-22 kbar) (P=10-50 kbar) (P=80-160 kbar)	4.61-∿3 3-2.5 3.5-4.2(Non-hydrostatic)				2040

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$LaTl_3$	1.57		$L1_2$		2274
$La_{0.2}Y_{0.8}$	2.70				2068
$La_{0.93}Yb_{0.07}$	3.56				2068
$Li_2Mo_6S_8$	4.2-3.5				2161
$Li_{2.6}O_4Ti_{1.5-2.7}$	10.9-11.4-10.9	HF			2146
$Li_{2.6}O_4Ti_{1.9}$	11.2	HF			2146
$Li_{2.6}O_4Ti_{1.7}$	11.4	HF			2146
$LiO_{3.95}Ti_2$	11.7	1970	$H1_1$		2391#
$Li_{1.1}O_{3.95}Ti_{1.9}$	9.6		$H1_1$		2391#
$Li_{1.05}O_4Ti_{1.95}$	12.0	1970	$H1_1$		2391#
$LiO_{3.9}Ti_2$	11.26 11.26-11.5(P=0-22 kbar)		$H1_1$		2148
$Li_2O_8Ti_4$	$\sim$11.4	HF			2378
$Li_{0.8}O_4Ti_{2.2}$	11.2-11.45(P=0-22 kbar)		$H1_1$		2148
LiO_4Ti	12.5		$H1_1$		2390
$Li_{1.05}O_4Ti_{1.95}$			$H1_1$	1.5	2390
$Li_{1.33}O_4Ti_{1.67}$			$H1_1$	1.5	2390
$Li_{2.6}O_4T_{1.3,4.0}$				4.2	2146
Lu	0.10	350			2084
Lu(P=45-190 kbar)	0.022-1.0				1996
$Lu_{1.2}Mo_6Se_8$	6.20-5.47		HEX		2050
$Lu_{0-0.58}Th_{1-0.42}$	1.36-1.8-1.4				2334
Mg(Flash evaporation, 50-1000A)				0.32	▽2192
$Mn_{0-0.012}NbSe_2$	7.4- <1		HEX		2176
$Mn_{0-0.07}Nb_3Sn$	T_c/T_{co}= 1-0.95		A15		2322
$Mn_{0.00047-0.0016}Pb$(Deposited 4.2K, 1600-4000A)	6.2-3.45				▽2247
$Mn_{0-0.004}Pb_{1-0.996}$(Deposited <3K, $\sim$500A)	7.2-4.4-4.8-<0.3 (Crystalline) 7-<0.3(Amorphous)				▽2364 ▽2095
Mn_xZn_{1-x}(Implant)					▽2095
$Mn_{0-45ppm}Zn$(Quench cond. 6K, $\sim$400A)	T_c'(-1.3)				▽2255

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Mo(99.995)	0.912				2217 2029
Mo(∿300A)	8.0	HF			∇2140
$Mo_{1-x}N_x$(Deposited <160K, ∿1000A)	∿8.5				∇2342
MoN_x	6.8	HF			∇2027
MoN_x	∿6.4	HF			∇2027
$MoN_{0-\sim0.33}$((RRR)4, N_2 in at 4.2K or room temp., 1500-3000A)	2.0-9.2 1.5-7.0		Data given		∇2143
$Mo_{1-0.77}N_{0-0.23}$(Implant, RRR=4.6)	9.4-<1.8				2382
$Mo_6Na_2S_8$	8.6-8.0				2161
$MoNa_xS_2$	3.6	HF			2273
$Mo_{0.02-0.95}Nb_{0.98-0.05}$	8.465-0.428(As cast)				2029
$Mo_{0-0.05}Nb_{1-0.95}$	9.2-7.8				2052
$Mo_{0.1-0.2}Nb_{0.765-0.61}Pd_{0.135-0.19}$	1.53-0.94-1.34				2257
$Mo_{0-0.2}Nb_{1-0.8}Se_2$	7.30-1.20		HEX		2293
$Mo_{0.03-0.20}Nb_{0.97-0.8}Se_2$	6.0-1.2		HEX		2100
$Mo_{0-0.1}Nb_{1-0.8}Zr_{0-0.1}$	9.130-7.775				2399#
$Mo_6Nd_2S_8$	3.45-3.2				2161
$Mo_6Nd_{1.0}Se_8$	8.22-7.65		HEX		2050
$MoNe_x$(Implant)				1.2	2382
$Mo_{0.18}Np_{0-0.73}U_{1-0.27}$	∿2-<0.05		CUB		2406
MoO_xXe_y	Data given				2382
MoOs	12.7-∿10.7(Order; S=0.91-0.57)		A15		2174
Mo_4P_3	2.5		ORTHO		1995
$Mo_{1-0.72}P_{0-0.28}$(Implant, RRR=4.54)	9.4-<1.8				2382
Mo_6PbS_8	14.7, 14.4		RHOMB		2137 2162
$Mo_{6.35}PbS_8$	12.6	HF	RHOMB		2408
Mo_6PbS_7(Irradiated 6K, neutrons)	12.30-4.8 ∿13.5(Annealed 11C)		RHOMB		2285

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Mo_6Pb_yS_{8-0}Se_{0-8}$	11.3-3.3-5.8-3.5		RHOMB		2038
$Mo_{6.3}PbS_6Se_2$	5.4	HF	RHOMB		2408
$Mo_{6.35}Pb_{0-1}S_8Sn_{1.2-0}$	11.8-10.1-12.8	HF	RHOMB		2408
$Mo_6PbS_{8-7}Te_{0-1}$	11.3-2.6		RHOMB		2038
$Mo_6Pb_{1.2}Se_8$	3.6		RHOMB		2408
Mo_6PbSe_7Te	4.0	HF	RHOMB		2408
$Mo_6Pb_ySe_{8-4}Te_{0-4}$	3.5-4.1-<2		RHOMB		2038
Mo_6PrSe_8	9.2, 9.16	HF	RHOMB(HEX)		2196 2050
$Mo_{0.85-0.55}Pt_{0-0.2}Re_{0.5-0.35}$	3.4-11.0				2252
$MoRb_{0.3}S_2$	6.9	HF			2273
Mo_6Rb_2S8				0.6	2161
$Mo_{0.95-0.7}Re_{0.05-0.3}$	1.461-11.015(As cast)				2029
$Mo_{0.85-0.70}Re_{0.15-0.30}$	6.6-9.1, 7.1-10.5 7.05-10.7, 7.3-11		A2		2252
$Mo_{0.3}Re_{0.7}$(Amorphous, sputtered)	7.62				2241
$Mo_{0.55-0.85}Re_{0.45-0.15}$ (Deposited 300-900C, 10,000-20,000A)	14.2-15-12.8				▽2302
$Mo_{0.7}Re_{0.3}$(10,000-20,000A)	15		A15		▽2302
$Mo_{0.98-0.6}Rh_{0.02-0.4}$(∼1000A)	∼7.8-8.2-5.5				▽2126
Mo_3S_4			RHOMB	1.1	2287 2408
$Mo_5S_6Sc_{1-2}$	2.6-2.8				2161
$Mo_5S_6Sc_{0.5}Sn$	11.4-12.0				2161
$Mo_6S_{4-0}Se_{4-8}$	2-6.2		RHOMB		2038
$Mo_3S_2Se_2$	2.1	HF	RHOMB		2408
$Mo_6S_8Sm_6$				0.6	2161
Mo_5S_8Sn(Irradiated 6K, neutrons)	12.06-5.9		RHOMB		2285
Mo_6S_8Sn	12.6, 13.3		RHOMB		2008 2121
Mo_5S_6Sn	10.8, 11.3	HF	RHOMB		2161 2317 2287

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Mo_{6.35}S_8Sn_{1.2}$	11.8	HF	RHOMB		2408
$Mo_5S_6SnTl_{0.5}$	9.3-8.1				2161
$Mo_5S_6SnY_{0.5}$	9.95-7.65				2161
MoS_2Sr_x	5.6	HF			2273
$Mo_5S_6Y_{0.5-2}$	2.5-2.6				2161
$Mo_6S_8Yb_2$	8.18-7.3				2161
Mo_5S_6Zn	3.0		RHOMB		2287
$Mo_{0.69-0.66}Sb_{0.31-0.34}$(Implant)	~1.7, 1.8				2382
Mo_3Se_4	6.3, 6.25		RHOMB		2287 2408
$Mo_6Se_8Sm_{1.2}$	6.83-6.35		HEX		2050
$Mo_6Se_8Tb_{1.2}$	5.70-5.34		HEX		2050
$Mo_6Se_{8-4}Te_{0-4}$	6.2-6.6-<5.5		RHOMB		2038
$Mo_6Se_8Tm_{1.2}$	6.33-5.68		HEX		2050
$Mo_6Se_8Y_{1.0}$	6.21-5.97		HEX		2050
$Mo_6Se_8Yb_{1.0}$	5.80-4.70		HEX		2050
Mo_5Se_6Zn			RHOMB	1.5	2287
$Mo_{0-0.7}Tc_{1-0.3}$	8.3-14.5-10-14-12				2267
$Mo_{0.5-0.7}Tc_{0.5-0.3}$	14-12		CUB		2267
$Mo_{0-0.3}Tc_{1-0.7}$	8.3-14.5		HEX		2267
$M_{0.4}Tc_{0.6}$	10		$D8_b$		2267
Mo_3Te_4			RHOMB	0.03	2287 2408
MoTi	0.2-4-2.8				2152 2256
$MoXe_x$(Implant)				1.2	2382
$N_{0-0.0007}Nb$	9.25-9.22				2209
NNb		HF			2310 2114
NNb(Fine powder)					2283
NNb	16-4	HF			▽2007
NNb	13.5-7.5	HF			▽2345
$N_{0-1.4}Nb$	8.5-<4.5-16-<4.5				▽2321

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
NNb(Deposited, ∿1000A)	14.67-8.85	HF			∇2366#
NNb(Implant, ∿2000A)	10				∇2016
$N_{0.884}Nb_{0.955}O_{0.069}$	13.3		B1		2036
$N_{0.955-0.967}O_{0.005-0.01}Zr_{0.982-0.967}$	9.5-8.7		B1		2036
$(NS)_x$(RRR>100)	0.33				2037
NS	0.28, 0.254, 0.24				2224 2063
NS(RRR=70)	0.29	HF			2136
NS	0.205, 0.235	HF			2124
NS					2231
NS(P=0-9 kbar)	0.33-0.54				2045
NS(Films on mylar)				0.02	∇2379
NTa	8.68		B1		2144
$N_{0-0.0038}Ta$	4.48-4.22	Type I to II			2209
$N_{\sim 0.5}Ta_{0.5}$	<4.2-8.15-<4.2		A1		∇2031
$N_{\sim 0.1}W_{0.9}$	<4.2-4.85-<4.2				∇2031
NxW	∿4.2, ∿4.7	HF			∇2027
NxW	4.1	HF			∇2027
$Na_{15}Pb_4$			CUB	1.5	2155
NaPb	6.1-6.2				2351
$NaPb_3$(β-form)	5.6	590, HF			2351#
$Na_{0.068}Pb_{0.932}$	6.68				2351#
$Na_{0-0.07}Pb_{1-0.93}$(100-1000A particles)		HF			2253
Nb(RRR-97, 223)	9.29. 9.27				2074
Nb(Marz grade)	9.164-9.126(As cast)				2029
Nb(99.99)	9.55(As rolled)				2178
Nb(99.99)	10.1(After 4 to 16 laser pulses)				2178
Nb(RRR=20)	9.255 9.415(Deformed 50%)				2244
Nb	9.130, 9.154				2399#

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Nb(<50 ppm O_2 <115 ppm intersticials)	9.30→9.36-9.28 (0→99% reduction by rolling)				2249
Nb(RRR=30.6)(O_2?)	9.25→9(Irradiated 400-1100C, fast neutrons)	HF			2377
Nb(Rolled foils)	9.55-10(0→16 laser pulses)				2169
Nb(Outgassed 2300C)		HF			2114 2331 2099
Nb(Irradiated oxygen ions at <20K)	T_c'(-0.07, -0.1				2177
Nb(Deposited ∿550C, ∿2500-4000A)	9.3→9.1				∇2221
Nb(Deposited-130 to 700C)	9→<4.2				∇2384
Nb(Deposited room temp., 14,400A to 27A)	9.3-2.0				∇2032
Nb_3Mo_xSn	T_c'(-0.7-0.6-1.3)				2052
$Nb_{0.60}Ni_{0.40}$(Liquid quenched)	1.5				2023
$Nb_{0.56}Ni_{0.16}Rh_{0.28}$(Liquid quenched)	3.3	HF			2023
$NbNi_{0-0.07}Se_2$	7-2-2.8-<1		HEX		2210
$Nb_{0.2}Np_{0-0.7}U_{1-0.3}$	∿2-<0.08		Data given		2406
$NbO_{1.00}$	1.61	147.6			2276#
$NbO_{1.02}$	1.38	HF			2276
$NbO_{0.96-1.02}$	1.37-1.55-1.38	129.7-143.6-131.0			2276#
$NbO_{0-0.00015}$	9.34-9.22	HF			2227
Nb_3Os	0.94		A15		2132#
Nb_3P	2.0		TET		1995
NbP(Co-sputtered)	6.0-5.6 4.8-6.8-5.6(Annealed 700C) 6.5-7.5-6(Annealed 750C)				∇2067
$Nb_3P_{0.15-0.9}Si_{0.85-0.1}$ (Co-sputtered)	5-7-6.5(Annealed 700C)				∇2067
Nb_3Pb(Simultaneous evap. room temp.)			A15	1.5	∇2346
$Nb_{0.66-0.70}Pb_{0.003-0.02}Sn_{0.34-0.29}$	17.8-18.0	HF			2374

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Nb_{0.8}Pd_{0.2}$	1.87-2.02				2071
$Nb_{0.9-0.65}Pd_{0.1-0.35}$	3.34-1.84		CUB		2257
$Nb_{0.72}Pd_{0.18}W_{0.1}$	1.57-1.44				2257
Nb_3Pt	9.20		A15		2132#
$Nb_{0.76}Pt_{0.24}$(Order 0.96 to 0.85)	10.7-7				2398
$Nb_{0.74-0.79}Pt_{0.26-0.21}$					2166
$Nb_{0.8}Rh_{0.2}$	2.65				2071
$Nb_{0.58}Rh_{0.42}$(Liquid quenched)	10.2		CUB		2024
$Nb_{0.58}Rh_{0.42}$(Microcrystalline)	∿4.8				2023
$Nb_{0.80-0.67}Ru_{0.20-0.33}$	0.39-<0.35				2061
$Nb_{\sim 0.7-0.5}Ru_{\sim 0.3-0.5}$ (∿1000A)	∿6-5				▽2126
NbS_2(P=1 bar-10 kbar)	5.9-5.9		HEX		1266 1853
Nb_3Sb	0.2				2272#
$NbSe_2$(See Table 3)					
$NbSe_2$	7.39	HF	HEX		2352
$NbSe_2$(RRR=30-35)	7.34, 7.29, 7.18	HF	HEX		2393
$NbSe_2$	7.3, 7.1	HF	HEX		2273 2226
$NbSe_2$	7.25, 7.2		HEX		2352# 2405# 2201# 2123#
$NbSe_2$	7.16-6.3	1260(2141#)	HEX		2181# 2141# 2386# 2405
$NbSe_2$	7.1	1280, 1200, HF	HEX		2386#
$NbSe_2$	6.3	943	HEX		2386#
$NbSe_2$(P=1 bar-17 kbar)	6.9-8.5		HEX		2373
$NbSe_2$(P=0-35 kbar)	7.11-∿9				2151
$NbSe_2$(P=1-20 kbar)	∿7.2-7.8		HEX		2234
$NbSe_3$			MONO	1.0	2361
$Nb_{0.94}Se_2Ti_{0.06}$	3.25		HEX		2293

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Nb_{0.97}Se_2Ti_{0.03}$	5.97		HEX		2293
$NbSe_2Ti_{300\ ppm}$	~7.19				2141#
$Nb_{1-0.7}Se_2V_{0-0.3}$	7.2-<1.5				2383
$Nb_{0.7}Se_2V_{0.3}$			HEX	1.5	2383
$NbSe_2Sn_{0-0.09}$	7-3		HEX		2210
$Nb_{0.83-0.68}Si_{0.17-\sim0.32}$ (Co-sputtered)	4.8-6.2-4.6-5.1(Annealed 800C) 4.4-5.5-3.2(Annealed 750C)				▽2067
$Nb_{0.78-0.91}Si_{0.225-0.086}$ (Chem. vapor deposition 800-900C)	8.05-7.35 4.30-3.55	HF	A15		2206
Nb_3Si(1 megabar implosion)	18.5-19 15-16 13-14		A15		2088 1998 2180
Nb_3Si	0.29	HF	TET		2237# 2088
NbSi(Sputtered, 650-750C)	8.6-4.65 5.2-6.5, 5.4				▽2395
$Nb_{0.74}Si_{0.26}$			(as prepared) (liquid quench)	<4.2 <4.2	2245
$Nb_{0.82}Si_{0.09}Sn_{0.09}$	5.6				2125
Nb_3Sn	17.9, Data given	HF	A15		2180 2389# 2166 2298# 2272#
Nb_3Sn		HF	A15		2107 2322 2375 2189
Nb_3Sn	17.6 17(After drawing) 12-13(After drawing)				2407
$Nb_{0.8}Sn_{0.2}$	18.2(Laser preparation)				2106
Nb_3Sn(0-99% reduction in area)	17.8-17.2				2109
Nb_3Sn(Irradiated fast neutrons)	18-14.5(Irradiated in superconductive state)				2396
Nb_3Sn(Irradiated <30K, oxygen ions)	16.3-4.4(Order 0.95-0.5)				2197
Nb_3Sn(Irradiated <30K, oxygen ions)	16-7.5	HF			2133
Nb_3Sn(Irradiated neutrons)	18-2.5(Order 0.98-0.6)	HF			2301 2019 2190

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Nb_{2.87}Sn$(Deposited 800C)	18.3-16.8				∇2289
$Nb_{2.72-3.69}Sn$(Deposited 700-800C)	18.3-11.4				∇2289
Nb_3Sn(In bending ∿1500A)	+0.1K to -0.1K (-20 to kp/mm^2)				∇2028
$Nb_{2.17-4.38}Sn$(Sputtered)	6.6-17.21		A15		∇2372
NbSn(Deposited 12,500-600A)	17.3-17.1				∇2135
Nb_3Sn(Deposited 800C, 4500A)			A15		∇2105
Nb_3Sn(Deposited 700-800C, 2000-3000A)	18.1-2.95(Irradiated helium ions)		A15		∇2118
Nb_3Sn(Deposited 560-750C, 1000-10,000A)	14-17.6				∇2246
Nb_3Sn(Vapor deposition, 50,000A)	7.3-3.5-41(Irradiated oxygen-ions)				∇2165
Nb_3Sn	18-2.95(Irradiated helium ions)		A15		∇2372
Nb_3SnTi_x	T_c'(+0.7+0.2)				2052
$Nb_{0.78-0.77}Sn_{0.22-0.22}Tl_{0.002-0.01}$	17.8-18.1	HF			2374
Nb_3SnZr_x	T_c'(-1.5+1.0)				2052
$Nb_{0.297}Ta_{0.702}$	5.26				2371
$NbTa_{0-20,000\ ppm}$		HF			2215
$Nb_{0.2}Ta_{0.4}Ti_{0.4}$(Weight fractions)	9.2				2048
$Nb_{1-0.95}Ti_{0-0.05}$(Weight fractions)	9.2-9.9-9.3				2052
$Nb_{0.34-0.8}Ti_{0.66-0.2}$	7-∿10	HF			2097
$Nb_{0.4}Ti_{0.6}$	9.19(As drawn-1.3x10^6) 9.19-9.35(Annealed				2030
$Nb_{0.2}Ti_{0.8}$(Laser pulse anneals)	6.9-5.2				2178 2169
$Nb_{0-0.11}Ti_{1-0.89}$					2256
$Nb_{0.5}Ti_{0.5}$(Foils, 50,000A, weight fractions)	T_c'(-0.13-0.09)(Irradiated < 30K oxygen ions)				2208
$Nb_{0.33}Ti_{0.66}Zr_{0-0.06}$		HF			2262
$Nb_{1-0.95}Zr_{0-0.05}$(Weight Fractions)	9.2-9.1-10.8				2052
$Nb_{0.75}Zr_{0.25}$	10.61(As drawn 3.0x10^5)				2030
$Nb_{0.75}Zr_{0.25}$	10.9				2026#
$Nb_{0.67}Zr_{0.33}$	11.2, 10.75 (Laser treated)				2106

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$Nb_{0.2-0.95}Zr_{0.8-0.05}$	7.907-10.853-10.5(Cast) 7.78-10.883-10.525(Annealed)				2029 2014 2139
$Ni_{0-0.0233}Tc_{1-0.977}$	7.85-7.25				2337
O_3Rb_xW	3.26-3.73(Thermal vapor growth at 1050C)				2142
$O_3Rb_{0.2}W$		HF			2142
O_xSn(∿100A)	T_c'(-)				▽2314
$O_{1.06}Ti$	0.94	HF			2276#
$O_{0.95}Ti$	0.65	HF			2276#
$O_{0.96-1.17}Ti$					2276#
$Os_{0.3,0.7}Re_{0.7,0.3}$			A3		2404#
$Os_{0.5}Tc_{0.5}$	4.3-4.2				2267
$Os_{0.25}Tc_{0.75}$	5.92		HEX		2267
P_3Rh_4	2.5		ORTHO		1995
PTa_3	0.4		TET		1995
PTh	≈0.2				2402
PZr_3	4.5		TET		1995
Pb(99.9999)	7.190				2399
Pb(Particles 100A)	Bulk Tc				2064
Pb(P=16-129 kbar)	6.53-3.74	661-318			2318
Pb(On PbTe, Te 0-130A)	<1.8-7.3	HF			▽2250
Pb(Evaporated on Si 60-100K 11-200A)	2.8-7.3				▽2220
Pb(17A, Extrapolated)	6.2				▽2172
Pb(Deposited ∿77K on glass, 330A-100A)	7.194-6.594				▽2200
PB(10,000A)	7.25_7				▽2164
Pb(∿50A, Plus ∿30A coat of Ge, Si, C, Zn, Bi, Mo, Se and PbTe)					▽2329
Pb(2700A)	7.20-7.15				▽2204
Pb("Bulk amorphous")	6.6				▽2172
Pb(Vapor quenched on mica)	6.65				▽2172
Pb(200-400A, on Cu 300-600A)	2.4-3.88				▽2248
Pb(∿2000A)	7.20				▽2228
Pb(250-11,000A)		HF			▽2066

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
PbSe(P≈300-340 kbar)	6.4-6.6				2086
PbTe(P≈175-260 kbar)	8-6.4				2086
PbTe($n=7\times10^{23}$ at 4.2K)	(Eddy currents produce effects thought to be superconductive at 20K)			2.0	2062 1884
PbTe(Pb, In, Tl, Al and Sn films on PbTe monocrystals, 0-8A)	$<$1-6.7				∇2218
$Pb_{0.4-0.8}Tl_{0.6-0.2}$(∼2000A)	4.6-6.80				∇2228
$Pd_{0.395}Rh_{0.605}$					2304#
$Pd_{0.25}Tc_{0.75}$	8.8-5		HEX		2267
$Pd_{0.30}Zr_{0.70}$	2.4	HF			2023
Pt(RRR 5000,6000)				0.04	2187
$PtTi_3$	0.49				2035#
$Pt_{0-0.3}Ti_{1-0.7}$	0.4-2.2-4.5-3-$<$1.2(As cast) 0.6-0.4(Annealed)				2035
PtV_3	2.63	HF	A15		2175
$Pt_{0.24}V_{0.76}$	2.70	HF	A15		2175
$Re_{0.88}W_{0.12}$			A3		2404#
$Re_{0.50}W_{0.50}$			$D8_b$		2404#
$Re_{0.05-0.75}W_{0.95-0.25}$			A2		2404#
$Rh_{0.5}Tc_{0.5}$	7.85-7.3-6.0		HEX		2267
$Rh_{0.25}Tc_{0.75}$	7.9-7.5-6.2		HEX		2267
$RhZr_2$	10.8	HF			2202
$Rh_{0-0.36}Zr_{1-0.64}$	6-6-11-11.5-10.5 6-4-8(As quenched)		(Rapid quench)		2021
$Rh_{0.23}Zr_{0.77}$(Liquid quench)	4.1	HF			2202
$Ru_{0.5}Tc_{0.5}$	7.5-7.0-4.2		HEX		2267
$Ru_{0.25}Tc_{0.75}$	8.1-7.15-5.6				2267
$Ru_{0-0.043}Tc_{1-0.957}$	7.85-7.07				2337
$Ru_{\sim0.45}Zr_{0.55}$(Evaporated ∼1000A)	2.8				2126
$S_{1.6}Se_{0.4}Ta$(See Table 3)					
$S_{1.6}Se_{0.4}Ta$	4.1	485, HF			2226 2386
$S_{1.6}Se_{0.4}Ta$(Monocrystals)	3.85	551, HF			2386# 2181
S_2Ta(See Table 3)					

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
S_2Ta	0.8		HEX(2H)		2405#
S_2Ta			HEX(4Hb)1.1		2405# 2386#
STh	0.49				2402
$Sb_{0.002}Sn_{0.998}$(Whiskers)	T_c'(0.6)(At 3% strain)				2235
Sb_xTl	T_c'(-0.001+0.022)				2101
ScSe	3.7				2402
$Sc_{0-0.5}Th_{1-0.5}$	1.36-1.75-0.95				2334
Se_2Ta(See Table 3)					
Se_3Ta(Fibrous, RRR ∿80)	2.1	HF	MONO		2291
SeTh	1.72				2402
SiV_3(RRR=17)	16.7(Monocrystal)	HF			2344 2189 2020
SiV_3	16.5				2272#
SiV_3	16.6(Monocrystal)				2271# 2238#
$Si_{0.227-0.26}V_{0.773-0.74}$	14.8-16.87		A15		2261
SiV_3(RRR=22)	16.9(Monocrystal)	HF			2009
$Si_{0.2-0.3}V_{0.8-0.7}$	14.5-17.2-15.8 13.0-16-10.1(Liquid quenched)				2245
Si_3V_5				0.076	2238#
SiV_3(P=0-29 kbar)	16.70-17.5				2039
SiV_3(Irradiated, helium ions)	16.5-2.2				▽2372 2019
$SiV_{\sim 3}$(Getter sputtered, ∿2500-4000A)	16.7-16.1				▽2221
$SiV_{\sim 3}$	∿4-16.7				▽2221
SiV_3(Sputtered)	3.5-17				▽2116
SiV_3(Deposited 700-800C, 2000-3000A)	16.8-2.2(Irradiated helium ions)		A15		▽2118
$SiV_{\sim 3}$(Deposited 650-1250C, 400-7650A)	15.8-12.2				▽2025
$SiV_{\sim 3}$(Deposited 1150C, 4875A)	15.8-15.4				▽2025
Sn(RRR=10,000)	T_c'(-, +)Deformed vs orientation				2385

TABLE 2 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Sn(Whiskers 0-0.67% strain)	3.7249-4.109	315-343, HF			2185 2235 2186 2185
Sn(99.9995, 54-500A)	4.027-3.792-3.932				▽2129
Sn(270-11,500A)	3.88-3.72	Data given			▽2066
Sn(730A, 1390A)	4.30, 4.59				▽2077
$Sn_{0.22-0.37}Tc_{0.78-0.63}$	7.4-6.4		HEX		2267
SnV_3	3.8				2272#
$Sn_{0-0.075}V_{1-0.925}$	5.43-1.3		CUB		2320
Ta(RRR=3900, 2400, 400)	4.53, 4.52, 4.50(Monocrystals)				2388
Ta	4.41		A2		2144
Ta(RRR=29)	4.415(Deformed 70%) 4.385				2244
TaV_2	3.6		C15		2313#
$Ta_{0.036}V_{0.964}$	4.55				2319#
$Ta_{0.056}V_{0.944}$	4.7	HF			2087
$Ta_{0.84-0.10}W_{0.16-0.90}$			A2		2404#
$Ta_{0.81}Zr_{0.19}$	6.5	HF			2303
$Ta_{0.71}Zr_{0.29}$	6.5	HF			2303
Tc(RRR=80)	7.85	HF			2337 2267
Tc(P=70-110 kbar)	7.4-6.8 7.35-6.7(Annealed)				2267
Tc(55-1600A)	6.2-5.9-7.7				▽2093
Tc(80A)	6.3	HF	CUB		▽2093
Tc(∿50,000A)	7.46				▽2164
$Tc_{0.97}Ti_{0.03}$	10.89-10.23		HEX		2001
$Tc_{0.85}Ti_{0.15}$	9.87-7.20(As cast) 8.10-7.73(Annealed)		A12		2001
TcTi			B2	1.7	2001
$Tc_{0-1}Ti_{1-0}$	∿0.4-10.89-∿7.8				2001
Te(P=1-3x10^{14})	2.0-4.2(P=40-60 kbar)				2083
Te(P=1-4x10^{18})	II 2.4-5.1(P=38-55 kbar) III 4.1-4.2(P=∿53-62 kbar) IV 4.72-4(P=63-80 kbar)				2083

TABLE 2(continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
Th	1.360				2400# 2335#
Th	1.38	160			2336
$ThU_{0.001}$	0.7	70(0.3K)			2336
$ThU_{0.0005}$	1.0	105(0.3K)			2336
$ThU_{0-0.00110}$	1.360-0.550				2335#
$Th_{1-0.3}Y_{0-0.7}$	1.36-1.65-0.8				2334
$Th_{1-0.85}Zr_{0-0.15}$	1.36-2.22				2334
$Ti_{0.97,\ 0.91}V_{0.03,\ 0.09}$	< 2.2, 3.7-4.3				2256
Tl	2.382	177.20			2047#
Tl(∿2000A)	2.36				▽2228
U(Alpha)	0.2-0.45				2277#
U(Alpha)	0.27, 0.20, 0.27				2277#
$U_{0.028}V_{0.972}$	4.16	HF			2242#
V(RRR=24)	5.24				2319# 2242#
V(RRR=10)	4.90 5.13(Deformed)				2244
V(Amorphous, ∿20-300A)	1.4-3	HF			▽2092
V(Crystalline, 60-500A)	3.3-4.5	HF			▽2092
V(Evaporated room temp. 100-2300A)	< 1.5-5	HF			▽2308 ▽2275
$V_{0.948}W_{0.052}$	4.08				2319#
V_2Zr	8.9	HF	C15		2081
V_2Zr	7.3		C15		2312#
W			A2		2404#
Zn(See Table 3)					
Zn(Whiskers many orientations)	T_c'(+0.07 to -0.04)(at 0.3% strain) T_c'(0.185 to -0.035)(at $4x10^8 N/m^2$)				2236
Zn(Quench condensed 6K)	0.83				▽2255
Zn(Quench condensed 6K, ∿400A)	1.51				▽2255
Zn(50-1000A)	1.4				▽2163

TABLE 3. Properties of Superconductive Materials with Organic and Related Constituents.

NOTE: "HF" signifies critical-magnetic-field data in Table 4.

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$NbSe_2$(ammonia)	0.6		HEX		2405
$NbSe_2$(cyclopentylamine)	0.90		HEX		2405
$NbSe_2$(cyclopropylamine)	1.1		HEX		2405
$NbSe_2$(dimethylamine)	3.0		HEX		2405
$NbSe_2$(ethylamine)$_{0.5}$	1.20		HEX		2405
$NbSe_2$(ethylene diamine)$_{0.25}$			HEX	0.35	2405
$NbSe_2$(ethylenediamine)$_{0.25}$	1.05		HEX		2386# 2405
$NbSe_2$(methylamine)$_{0.5}$	0.95		HEX		2405
$NbSe_2$(triethylamine)			HEX	1.3	2405
$S_{1.6}Se_{0.4}Ta$(pyridine)$_{0.5}$	2.30	194	HEX		2386#
$S_{1.6}Se_{0.4}Ta$(pyridine)$_{0.5}$		175,(HF data given			2386
S_2Ta(ammonia)	5.0 3.8		HEX(4H) HEX(2H)		2405 2405
S_2Ta(aniline)$_{0.75}$	2.9	(HF data given)			2226
S_2Ta(collidine)$_{0.167}$	2.80(Monocrystal)		HEX		2386#
S_2Ta(cyclopentylamine)	3.15		HEX		2405
S_2Ta(cyclopropylamine)	3.0		HEX		2405
S_2Ta(dimethylamine	3.4 3.8		HEX(2H) HEX(4H)		2405 2405
S_2Ta(deuterium)$_{0.05}$			HEX		2386#
S_2Ta(ethylamine)$_{0.5}$	3.5 3.4		HEX(4H) HEX(2H)		2405 2405
S_2Ta(ethylenediamine)$_{0.25}$	 3.2 4.7		HEX HEX(4H) HEX(1T) HEX(2H)	 0.35 	2386# 2405# 2405 2405
S_2Ta(methylamine)$_{0.5}$	5.6 4.6		HEX(2H) HEX(4H)		2405 2405
S_2Ta(pyridine)$_{0.5}$	3.30(Monocrystal) 3.2 3.47 3.45(Monocrystal)	 (HF data given) 	HEX(2H) HEX(4H) 		2386 2405 2226 2181

TABLE 3 (continued)

Material	T_c(K)	H_o (oersted)	Crystal Structure	T_n(K)	Refs.
$S_2Ta(pyridine)_{1/2}$(plus S)		208 (HF data given)			2386
S_2Ta(triethylamine)	1.3		HEX(4H)		2405
			HEX(2H)	1.3	2405
$Se_2Ta(ethylenediamine)_{0.25}$	0.95		HEX		2405
Zn(zinc etioprophyrin)	2.0				$^{\nabla}$2163

TABLE 4. Critical Magnetic Fields H_{c1}, H_c, H_{c2} and H_{c3} of Superconductive Materials (Mainly Type II).

NOTE: Magnetic fields in kilooersteds.

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
$Ag_{0-0.02}Nb_{0.33}Ti_{0.66}$				117-110		4.2	2262
$Al_2Ce_{0.00626}La_{0.994}$	1.3			0-0.042-0		0.15-1.3	2098
$Al_2Ce_{0.0066-0.009}La$	~1.5-0.2			Data given			2332
$AlCe_{0-0.017}La_{3-2.983}$	6-0.8			Data given			2333
$Al_{0-0.08}Ga_{0.2-0.12}V_3$	15-14.1			205-210-195		4.2	2010
AlIn	2.282, 3.178			Data given			$^{\nabla}$2211
Al_2La	3.3			2.5		0	2332
$Al_{0-0.6}Mo_{6.35}S_8Sn_{1.2}$	11.8-14.3			325-560 (Estimated)		0	2408 2089
$AlNb_3$	≃17.5			Data given			2193
Al_3Nb	0.64			0.70		0.56	2170
$AlNb_2$	0.74			0.31		0.68	2170
$Al_{0-0.15}Nb_{1-0.85}$	9.03-5.15(Cast) 8.8-8.1-10.0			19-22-8.5 3.9-20.8-11.6		4.2 4.2	2049
$Al_{0-0.1}Nb_3Sn_{1-0.9}$	17.8-18.0-17.9			230-290-280		4.2	2374
$Al_xNb_3Sn_{1-x}$	~16.6			~195		0	2108
$Al_{0-0.025}Nb_{0.33}Ti_{0.66}$	9.1-8.2			118-102		4.2	2262
$Al_{0-0.265}V_{1-0.735}$	5.43- < 0.5			Data given			2320
$As_{0.04}Ge_{0.15}Te_{0.81}$	0.90-0.88			3.4, 6		0	2330
$AsNb_3$	~0.31			0.22		0.2	2237
$Au_{0.24}La_{0.76}$(Liquid quenched)	3.3(Amorphous)			55		0	2023
	4.05(Crystalline)			38		0	
$Bi_{0.22}In_{0.78}$	4.53, 5.61			Data given			2243
$Bi_{0-0.05}In_{1-0.95}$	3.4-4.27	0.3-0.32		0.6-1.6		0	2102
$Bi_{0-0.016}In_{1-0.984}$		0.276-0.28		0.28-1.6		0	2355
$Bi_{0.016-0.05}In_{0.986-0.95}$		0.28-0.35	0.28-0.60				
$Bi_{0-0.3}Pb_{1-0.7}$	7.2-8.65-7.9			Data given	Data given		2110
$C_{1.3-1.6}La$	11.1	0.022		95		4.2	2219

TABLE 4 (continued)

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
$C_{1.55}Th_{0.3}Y_{0.7}$	17.1			280		0	2188
Ca_xMoS_2	4.0			74(Parallel) 13 65 2.1(Perpend.)		0 2.4 0 2.4	2273
$Ce_{0.2}La_{0.8}Mo_6Se_8$	8.9			292 220		0 4.2	2196
$Ce_{0.004}La_{0.80}Th_{0.20}$	3.6			11		0	2167
$Ce_{0-0.0075}La_{0.80}Th_{0.20}$ (Re-entrant)	5.25- < 0.045			Data given			2167
$Ce_xLa_{3-x}Y$				Data given			2360
$CeRu_2$	6.28		1.2	50		0	2096
$Co_{0.075}NbSe_2$	4.5			Data given			2225
$Cs_{0.1}F_{0.1}O_{2.9}W$	4.87-4.94			1.3-1.72(Perpend.)		0	2046
$Cs_{0.3}MoS_2$	6.9			220 94.5(Parallel) 33 16(Perpend.)		0 4.1 0 4.1	2273
$CuMo_3S_4$	10.6, 10.4			45		8.8	2408
$Cu_2Mo_6S_8$	10.4			130		0	2408
$Cu_{0.7}Mo_3Se_4$	5.8			65		3.6	2408
$Cu_{0-0.03}Nb_{0.33}Ti_{0.66}$	9.3-8.8-9.2			117-114-118		4.2	2262
$D_{0-1}HfV_2$	9.7-3.4			Data given			2122
D_2HfV_2	5.8			40		2	2339
$Eu_{0.2}La_{0.8}Mo_6Se_8$	10.7-11.4			350		4.2	2196
$Eu_{0.1-0.8}Mo_{6.35}S_8Sn_{1.1-0.24}$	11.5			300-370-340		0	2408
$Fe_{0.3}HfV_{1.7}$	5			70		3	2081
$Fe_{0.15}HfV_{1.85}$	9.5			125		7	2081
$Fe_{0-0.05}Nb_{0.76}Pt_{0.24-0.19}$	8.56-1.80(Disordered) 10.10-1.40(Ordered)			145-20 ~145-20		0 0	2398
$Fe_{0-0.04}Nb_{0.76}Pt_{0.24-0.19}$				105-15(Disordered) 115-22(Ordered)			2398
$Fe_{0.034}Nb_3Sn$	17			265		0	2322
$Fe_{0.017}Nb_3Sn$	17.5			260		0	2322

TABLE 4 (continued)

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
$Fe_{0-0.10}S_2Ta$	0.8-3.3- < 1.3			~32(Parallel) 2.4(Perpend.)		1.6	2225
$Fe_{0.05}S_2Ta_{0.95}$	3.2-2.7			Data given			2042
$Fe_{0.3}V_{1.7}Zr$	4.4			40		3	2081
$Ga_{0.5}Mo_5S_6Sn$		~3(0.5T_c)	75(0.5T_c)	125(0.75T_c)			2089
$Ga_{0.5}Mo_5S_6Sn$	13.5-4(P=0-100 kbar)			(H_{c2} decreases with P increase)			2317
$Ga_{0.01-0.04}Nb_{0.73-0.82}Sn_{0.26-0.14}$	17.8-18.1-18.0			230-300		4.2	2374
GaV_3(Irradiated and non-irradiated)				Data given			2381
$Gd_{0.4}Mo_{6.35}Pb_{0.6}S_8$	4.9			105		1	2408
$Gd_{0.6}Mo_{6.35}Pb_{0.4}S_8$	3.0			6		2.5-1	2408
$Gd_{0.6}Mo_{6.35}S_8Sn_{0.6}$	6.7			55		1.2	2408
$GeNb_3$(Deposited ~740C, 600-15,000A)	22.7 Max.			33 36(Perpend.) 25 45(Parallel) (10,000A/2240A)		20	∇2309
$GeNb_3$	10.5-7.5			340-370		0	2007
$Ge_{\sim0.25-0.14}Nb_{0.75-0.86}$ (Deposited 750-1000C)	22.3-20.7(Sputtered) 18.2-22-21(Chem. Vapor Deposition)			255-390 260-330		0	∇2367 ∇2341
$GeNb_3$(Granular)				360-340		0	∇2345
$Ge_{0-0.02}Nb_{0.33}Ti_{0.66}$	8.9-8.2			115-118-110		4.2	2262
$Ge_{0.01,0.05,0.45}Te_{0.99,0.95,0.55}$	0.40-0.51			Data given			2330
$H_{0-1.6}HfV_2$	9.7-2.2			(Data given, $HfV_2H_{0.5}$)			2122
HPd	9.62			0.98		0	2349
$H_{1-0.933}Pd$	9.62-5.5			Data given			2349
$Hf_{0.26}Nb_{0.74}$	9.3	0.9(4.14K)		70 74.5		1.6 0	2222#
HfV_2	9.7			120		7.2	2339
HfV_2	9.3			120		7	2081
HfV_2	9.2			268 200		0 4.2	2005
$Hf_{0.15-0.6}V_{0.85-0.4}$	9-9.3-8.4			150-220-180		4.2	2005

TABLE 4 (continued)

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
$Hf_{0.55}V_2Zr_{0.45}$				240		4.2	2005
$Hf_xV_yZr_{1-x-y}$	10.1-7.8			240-85		4.2	2005
$Hf_{0.5}V_2Zr_{0.5}$	10.1			275 230		0 4.2	2005#
$Hf_{0.4-0.3}VZr_{0.6-0.7}$	10.2			254(Extrapolated) 208		1.7 4.2	2183
$Hf_{0-1}V_2Zr_{1-0}$	8.5-10.1-9.2			105-240-200		4.2	2005
Hg(300-10,880A)	T_c'(∿-0.2)			Data given			∇2091
In(Type I to Type II)	Data given			Data given			∇2065
In(On Pb Te, 15-340A)	2.2-∿5.5			Data (perpend.) Shown(Parallel)			∇2250
$In_{0.98-0.874}Mg_{0.02-0.126}$				0.46-1.25		0	2104
$In_{0.01-0.04}Nb_{0.78-0.73}Sn_{0.21-0.23}$	17.8-18.1			230-290		4.2	2374
$In_{0.05}Nb_3Sn_{0.95}$(Nominal)				270-280(Sn bath) 230-280(Sn, Cu bath)		4.2 4.2	2374
$In_{0.17}Pb_{0.83}$				1.4		4.2	2375
$In_{0.013-0.10}Pb_{0.987-0.90}$				Data given	Data given		2103
$InSn_4$	4.54			1.349(Parallel a) 1.219(Parallel c)		0 0	2326
InTl(Superimposed films)				Data given			∇2211
$Ir_{0.38}V_{0.62}$	1.94			21.6		0	2175
$K_{0.4}MoS_2$	6.9			40(Perpend.)		0	2273
La(Deposited ≃150K, 5000, 10,000A)	4.90			12.5(Perpend.) 5.2(Parallel)		2.6 4.2	∇2145
$La_{0.2}Mo_{6.35}Pb_{0.8}S_8$	13.2			560 480		0 4.2	2408
$LaMo_6S_8$	11.3			463 370		0 4.2	2196
$LaOs_2$	9		1.6	30		0	2096
La_3Se_4($n=1.20-3.67x10^{21}$)	2.60-6.86	0.0223- 0.1192	0.0742- 0.340			0	2079#
$Li_{2.6}O_4Ti_{1.9}$	11.2			185		4.2	2146
$Li_{2.6}O_4Ti_{1.5-2.7}$	10.9-11.4-10.9			123-185-77		4.2	2146
$Li_{2.6}OTi_{1.7}$	11.4			162 183		4.2 0	2146

TABLE 4 (continued)

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
$Li_2O_8Ti_4$	$\simeq$11.4			>70		4.2	2378
Mo($\sim$300A)	8.0			80 $\simeq$250(GLAG Theory)		6.4 0	$^{\nabla}$2140
MoN_x	6.8, $\sim$6.4			55		4.2	$^{\nabla}$2027
$MoNa_xS_2$	3.6			50 23(Parallel) 7.6 3.2(Perpend.)		0 2.2 0 2.2	2273
$Mo_{6.35}PbS_8$	12.6			540 450		0 4.2	2408
$Mo_{6.3}PbS_6Se_2$	5.4			130 70		3 4.2	2408
$Mo_{6.35}Pb_{0-1}S_8Sn_{1.2-0}$	11.8-10.1-12.8			395-325-540		0	2408
Mo_6PbSe_7Te	4.0			54		2.6	2408
Mo_6PrSe_8	9.2			204 144		0 4.2	2196
$MoRb_{0.3}S_2$	6.9			40(Perpend.)		0	2273
$Mo_3S_2Se_2$	2.1			40		1.2	2408
$Mo_{6.35}S_8Sn_{1.2}$	11.8			330		0	2408 2317
MoS_2Sr_x	5.6			46(Parallel) 20 13.6(Perpend.) 6.3		0 3.4 0 3.4	2273
NNb				4.06-4.63		4.2	2114
NNb	16-4			180-260-210		0	$^{\nabla}$2007
NNb	16			180		0	$^{\nabla}$2007
NNb	9			260		0	$^{\nabla}$2007
NNb	13.5-7.5			280-250		0	$^{\nabla}$2345
NNb($\sim$1000A)	14.67-8.85			139-214		0	$^{\nabla}$2366#
NS(RRR=70)	0.29			8.1(Parallel) 0.87(Perpend.)		0	2136 2124
$N_{0-0.0038}Ta$	4.48-4.22	Data given	0.828-0.784			0	2209
NW_x	4.1			42		1.7	$^{\nabla}$2027
$NaPb_x$(Particles 100-1000A)				Data given			2253

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
Nb(RRR 30.6)	9.25-9(Irradiated fast neutrons)			3.05-3.05-5.05		4.2	2377 2331
Nb(Outgassed 2300C)				2.74		4.2	2114
Nb		1.44 1.21			2.83 3.10	4.2	2099
$Nb_{0.56}Ni_{0.16}Rh_{0.28}$	3.3			34		2.2	2023
$NbO_{1.02}$	1.38	0.06		0.14		0.8	2276
$NbO_{0-0.00015}$	9.34-9.22			Data given	Data given		2227
$Nb_{0.66-0.70}Pb_{0.003-0.02}Sn_{0.34-0.29}$	17.8-18.0			230-290		4.2	2374
$Nb_3Pb_{0.05}Sn_{0.95}$(Nominal)				190-280(Sn bath) 220-260(Cu Sn bath)		4.2	2374
$NbSe_2$(RRR=30-35)	7.18-7.39(Monocrystals)			145(Parallel) 44-46(Perpend.)		0 0	2393
$NbSe_2$	7.3			140(Parallel) 68 40(Perpend.) 21		0 4.4 0 4.4	2273 2226
$Nb_{0.78-0.91}Si_{0.225-0.086}$ (Deposited 800-900C Chem. vapor)	8.05-7.35			19.3-14.9		4.2	2206
Nb_3Si	0.29			0.097-0.112		0	2237#
Nb_3Sn	18			255		0	2322 2189
Nb_3Sn		0.31				1.35	2375
Nb_3Sn(Irradiation < 30K Oxygen ions)	7.5-16			75-155		0	2133
Nb_3Sn(Irradiated neutrons)	18-2.5(Order from 0.98-0.6)			230-40		0	2301
$Nb_{0.78-0.77}Sn_{0.22-0.22}Tl_{0.002-0.01}$	17.8-18.1			230-300		4.2	2374
$Nb_{1-x}Ta_x$				Data given			2215
$Nb_{0.33}Ti_{0.66}Zr_{0-0.06}$				114-107-108		4.2	2262
$O_3Rb_{0.2}W$				48(Parallel c) 17.3,6.9(Perpend. c, phi=0°,30°)		0	2142
$O_{1.06}Ti$	0.94			32.9		0	2276
$O_{0.95}Ti$	0.65			30.5		0	2276

TABLE 4 (continued)

Material	T_c(K)	H_{c1}	H_c	H_{c2}	H_{c3}	T_{obs}	Refs.
Pb(on PbTe,Te)(0-1304)	<1.8-7.3			Data shown			∇2250
$Pd_{0.30}Zr_{0.70}$(Liquid quenched)	2.4			16		1.8	2023
PtV_3	2.63			35.1		0	2175
$Pt_{0.24}V_{0.76}$	2.70			29.9		0	2175
$RhZr_2$	10.8			106.5		0	2202
$Rh_{0.23}Zr_{0.77}$(Liquid quench)	4.1			80.1		0	2202
$S_{1.6}S_{0.4}Ta$	4.1			Data given			2226 2386
$S_{1.6}Se_{0.4}Ta$				Data given			2181
$S_2Ta(Pyridine)_{1/2}$	3.47			Data given			2226 2386
$S_2Ta(Aniline)_{3/4}$	2.9			Data given			2226
Se_3Ta(RRR∿80)	2.1			Data given			2291
SiV_3(RRR=17)	16.7(Monocrystal)			60		14	2344 2189 2020
SiV_3(RRR=22)	16.9(Monocrystal)	0.77 0.72				0 4.2	2009
Sn(Whiskers)	3.73			Data given			2186
$Ta_{0.056}V_{0.944}$	4.7			≃10		0	2087
$Ta_{0.81}Zr_{0.19}$	6.5			15		2	2303
$Ta_{0.71}Zr_{0.29}$	6.5			16		2	2303
Tc(RRR=100)	6.3-7.1-7.8			Data given			2267#
Tc(80A)	6.3			34		5.6	∇2093
$U_{0.028}V_{0.972}$	4.16			∿50		0	2242#
V(Amorphous, ∿20-300A)	1.4-3			55		0	∇2092
V(Deposited Room temp. 500-2300A)	2.5-5, <1.5-4.5			4.0-4.8-2.46(Parallel) 1.98-2.9-4.0(Perpend.)		4.2	∇2308
V_2Zr	8.9			95		6	2081

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16. ABSTRACT (*A 200-word or less factual summary of most significant information. If document includes a significant bibliography or literature survey, mention it here.*)

This report includes data on additional superconductive materials extracted from the world literature up to fall 1977 and is an addendum to the data set published in J. Phys. Chem. Ref. Data 5, #3, 581-821 (1976) (Reprint #84). The data presented are new values and have not been selected or compared to values (except for selected values of the elements) previously assembled by the Superconductive Materials Data Center. The properties included are composition, critical temperature, critical magnetic field, crystal structure and the results of negative experiments. Special tabulations of high magnetic field materials with Type II behavior and materials with organic components are included. All entries are keyed to the literature. A list of recent reviews centered on superconductive materials is included.

17. KEY WORDS (*six to twelve entries; alphabetical order; capitalize only the first letter of the first key word unless a proper name; separated by semicolons*)

Bibliography; composition; critical fields; critical temperature; crystallographic data; data compilation; low temperature; superconductive materials; superconductivity.

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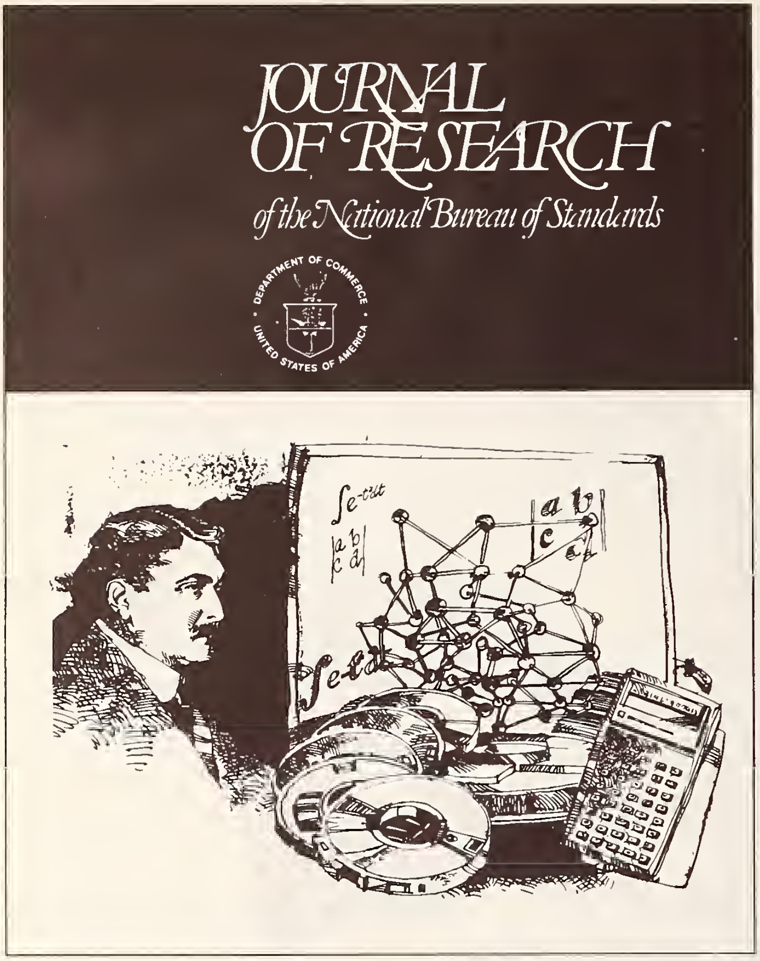

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NOTE: At present the principal publication outlet for these data is the Journal of Physical and Chemical Reference Data (JPCRD) published quarterly for NBS by the American Chemical Society (ACS) and the American Institute of Physics (AIP). Subscriptions, reprints, and supplements available from ACS, 1155 Sixteenth St. N.W., Wash., D.C. 20056.

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